



HESTORE.HU

elektronikai alkatrész áruház

EN: This Datasheet is presented by the manufacturer.

Please visit our website for pricing and availability at www.hestore.hu.

High-Voltage Input Integrated Switch Step-Down Regulator

Features:

- Up to 96% Efficiency
- Input Voltage Range: 4.4V to 50V
- Output Voltage Range: 2.0V to 24V
- 2% Output Voltage Accuracy
- Qualification: AEC-Q100 Rev. G, Grade 1(-40°C to 125°C)
- Integrated N-Channel Buck Switch: 600 mΩ
- Minimum 500 mA Output Current Over All Input Voltage Range (See [Figure 2-9](#) for Maximum Output Current vs. V_{IN})
 - Up to 1.2A Output Current at 3.3V and 5V V_{OUT} , $V_{IN}>12V$, SOT-23 package at 25°C ambient temperature
 - Up to 0.8A Output Current at 12V V_{OUT} , $V_{IN}>18V$, SOT-23 package at 25°C ambient temperature
- 500 kHz Fixed Frequency
- Adjustable Output Voltage
- Low Device Shutdown Current
- Peak Current Mode Control
- Internal Compensation
- Stable with Ceramic Capacitors
- Internal Soft-Start
- Internal Pull-Up on EN
- Cycle-by-Cycle Peak Current Limit
- Undervoltage Lockout (UVLO): 4.1V to Start; 3.6V to Stop
- Overtemperature Protection
- Available Package: 6-Lead SOT-23, 8-Lead 2x3 TDFN

Applications:

- PIC[®] MCU/dsPIC[®] DSC Microcontroller Bias Supply
- 48V, 24V and 12V Industrial Input DC-DC Conversion
- Set-Top Boxes
- DSL Cable Modems
- Automotive
- AC/DC Adapters
- SLA Battery Powered Devices
- AC-DC Digital Control Power Source
- Power Meters
- Consumer
- Medical and Health Care
- Distributed Power Supplies

General Description:

The MCP16331 is a highly integrated, high-efficiency, fixed frequency, step-down DC-DC converter in a popular 6-pin SOT-23 or 8-pin TDFN 2x3 package that operates from input voltage sources up to 50V. Integrated features include a high side switch, fixed frequency Peak Current Mode Control, internal compensation, peak current limit and overtemperature protection. Minimal external components are necessary to develop a complete step-down DC-DC converter power supply.

High converter efficiency is achieved by integrating the current-limited, low-resistance, high-speed N-Channel MOSFET and associated drive circuitry. High switching frequency minimizes the size of external filtering components resulting in a small solution size.

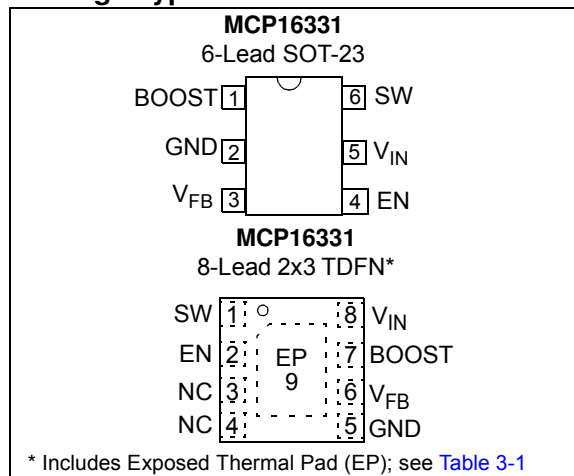
The MCP16331 can supply 500 mA of continuous current while regulating the output voltage from 2.0V to 24V. An integrated, high-performance peak current mode architecture keeps the output voltage tightly regulated, even during input voltage steps and output current transient conditions that are common in power systems.

The EN input is used to turn the device on and off. While off, only a few μA of current are consumed from the input for power shedding and load distribution applications. This pin is internally pulled up, so the device will start even if the EN pin is left floating.

Output voltage is set with an external resistor divider.

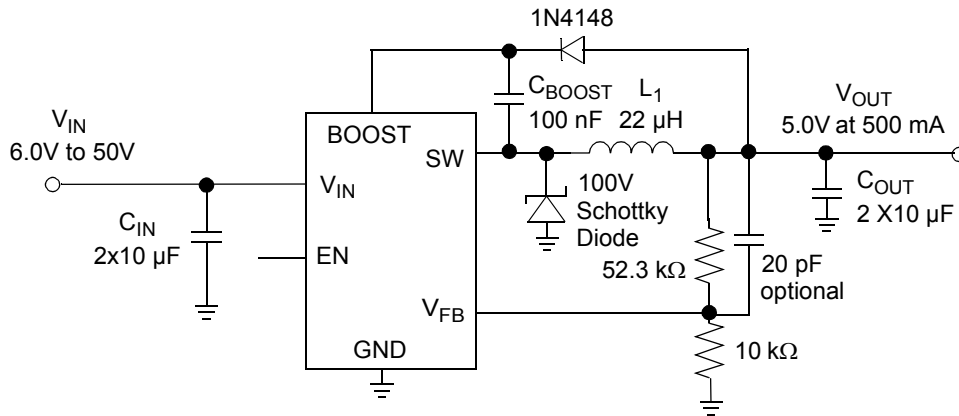
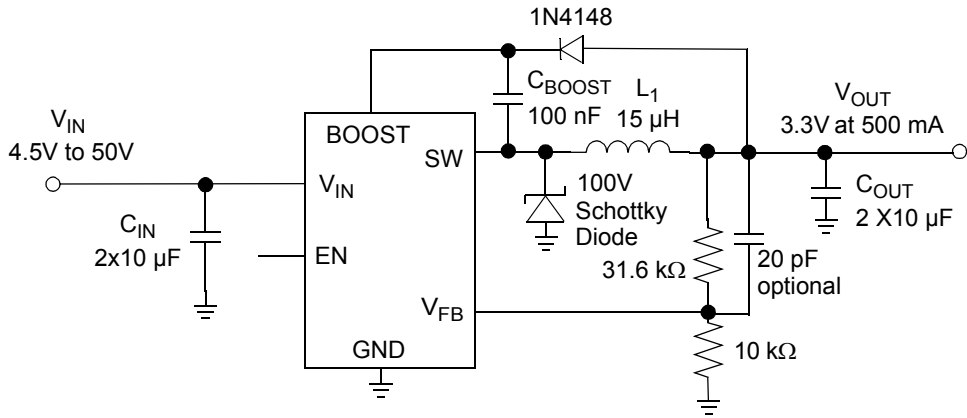
The MCP16331 is offered in a space saving 6-Lead SOT-23 and 8-Lead 2x3 TDFN surface mount package.

Package Type

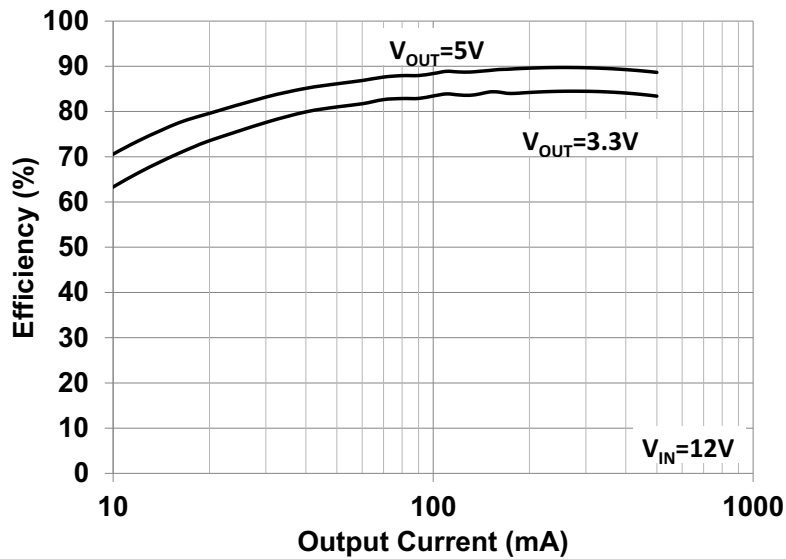


MCP16331

Typical Applications



Note: EN has an internal pull up, so the device will start even if the EN pin is left floating



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

$V_{IN, SW}$	-0.5V to 54V
BOOST – GND	-0.5V to 60V
BOOST – SW Voltage.....	-0.5V to 6.0V
V_{FB} Voltage	-0.5V to 6.0V
EN Voltage	-0.5V to ($V_{IN} + 0.3V$)
Output Short Circuit Current	Continuous
Power Dissipation	Internally Limited
Storage Temperature	-65°C to +150°C
Ambient Temperature with Power Applied ...	-40°C to +125°C
Operating Junction Temperature.....	-40°C to +160°C
ESD Protection on All Pins:	
HBM.....	4 kV
MM	300V

† **Notice:** Stresses above those listed under “Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^\circ\text{C}$, $V_{IN} = V_{EN} = 12V$, $V_{BOOST} - V_{SW} = 3.3V$, $V_{OUT} = 3.3V$, $I_{OUT} = 100\text{ mA}$, $L = 15\ \mu\text{H}$, $C_{OUT} = C_{IN} = 2 \times 10\ \mu\text{F}$ X7R Ceramic Capacitors
Boldface specifications apply over the T_A range of -40°C to $+125^\circ\text{C}$.

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
Input Voltage	V_{IN}	4.4	—	50	V	Note 1
Feedback Voltage	V_{FB}	0.784	0.800	0.816	V	
Output Voltage Adjust Range	V_{OUT}	2.0	—	24	V	Note 1, Note 3
Feedback Voltage Line Regulation	$ \Delta V_{FB}/V_{FB} /\Delta V_{IN}$	—	0.002	0.1	%/V	$V_{IN} = 5V$ to $50V$
Feedback Voltage Load Regulation	$ \Delta V_{FB}/V_{FB} $	—	0.13	0.35	%	$I_{OUT} = 50\text{ mA}$ to 500 mA
Feedback Input Bias Current	I_{FB}	—	+/- 3	—	nA	
Undervoltage Lockout Start	$UVLO_{STRT}$	—	4.1	4.4	V	V_{IN} Rising
Undervoltage Lockout Stop	$UVLO_{STOP}$	3	3.6	—	V	V_{IN} Falling
Undervoltage Lockout Hysteresis	$UVLO_{HYS}$	—	0.5	—	V	
Switching Frequency	f_{SW}	425	500	550	kHz	
Maximum Duty Cycle	DC_{MAX}	90	93	—	%	$V_{IN} = 5V$; $V_{FB} = 0.7V$; $I_{OUT} = 100\text{ mA}$
Minimum Duty Cycle	DC_{MIN}	—	1	—	%	Note 4
NMOS Switch On Resistance	$R_{DS(ON)}$	—	0.6	—	Ω	$V_{BOOST} - V_{SW} = 5V$, Note 3
NMOS Switch Current Limit	$I_{N(MAX)}$	—	1.3	—	A	$V_{BOOST} - V_{SW} = 5V$, Note 3
Quiescent Current	I_Q	—	1	1.7	mA	$V_{IN} = 12V$; Note 2
Quiescent Current - Shutdown	I_Q	—	6	10	μA	$V_{OUT} = EN = 0V$
Output Current	I_{OUT}	500	—	—	mA	Note 1; see Figure 2-9
EN Input Logic High	V_{IH}	1.9	—	—	V	

Note 1: The input voltage should be > output voltage + headroom voltage; higher load currents increase the input voltage necessary for regulation. See characterization graphs for typical input to output operating voltage range.

2: V_{BOOST} supply is derived from V_{OUT} .

3: Determined by characterization, not production tested.

4: This is ensured by design.

MCP16331

DC CHARACTERISTICS (CONTINUED)

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^\circ\text{C}$, $V_{IN} = V_{EN} = 12\text{V}$, $V_{BOOST} - V_{SW} = 3.3\text{V}$, $V_{OUT} = 3.3\text{V}$, $I_{OUT} = 100\text{ mA}$, $L = 15\ \mu\text{H}$, $C_{OUT} = C_{IN} = 2 \times 10\ \mu\text{F X7R Ceramic Capacitors}$
Boldface specifications apply over the T_A range of -40°C to $+125^\circ\text{C}$.

Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
EN Input Logic Low	V_{IL}	—	—	0.4	V	
EN Input Leakage Current	I_{ENLK}	—	0.007	0.5	μA	$V_{IN} = EN = 5\text{V}$
Soft-Start Time	t_{SS}	—	600	—	μs	EN Low-to-High, 90% of V_{OUT}
Thermal Shutdown Die Temperature	T_{SD}	—	160	—	$^\circ\text{C}$	Note 3
Die Temperature Hysteresis	T_{SDHYS}	—	30	—	$^\circ\text{C}$	Note 3

- Note 1:** The input voltage should be $>$ output voltage + headroom voltage; higher load currents increase the input voltage necessary for regulation. See characterization graphs for typical input to output operating voltage range.
- 2:** V_{BOOST} supply is derived from V_{OUT} .
- 3:** Determined by characterization, not production tested.
- 4:** This is ensured by design.

TEMPERATURE SPECIFICATIONS

Electrical Specifications:						
Parameters	Sym.	Min.	Typ.	Max.	Units	Conditions
Temperature Ranges						
Operating Junction Temperature Range	T_J	-40	—	+125	$^\circ\text{C}$	Steady State
Storage Temperature Range	T_A	-65	—	+150	$^\circ\text{C}$	
Maximum Junction Temperature	T_J	—	—	+160	$^\circ\text{C}$	Transient
Package Thermal Resistances						
Thermal Resistance, 6L-SOT-23	θ_{JA}	—	190.5	—	$^\circ\text{C/W}$	EIA/JESD51-3 Standard
Thermal Resistance, 8L-2x3 TDFN	θ_{JA}	—	52.5	—	$^\circ\text{C/W}$	EIA/JESD51-3 Standard

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $V_{IN} = EN = 12V$, $C_{OUT} = C_{IN} = 2 \times 10 \mu F$, $L = 15 \mu H$, $V_{OUT} = 3.3V$, $I_{LOAD} = 100 \text{ mA}$, $T_A = +25^\circ C$, 6-Lead SOT-23 package.

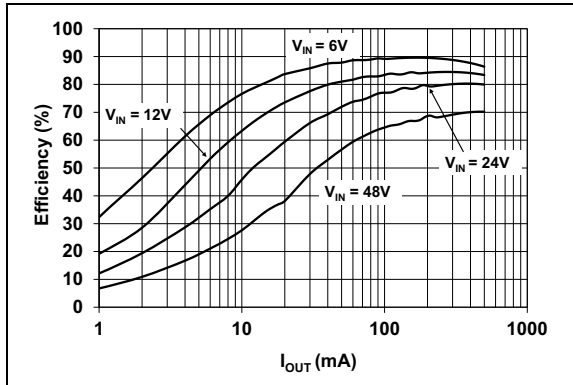


FIGURE 2-1: 3.3V V_{OUT} Efficiency vs. I_{OUT} .

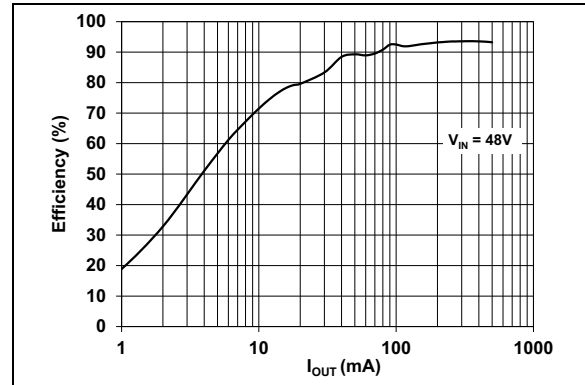


FIGURE 2-4: 24V V_{OUT} Efficiency vs. I_{OUT} .

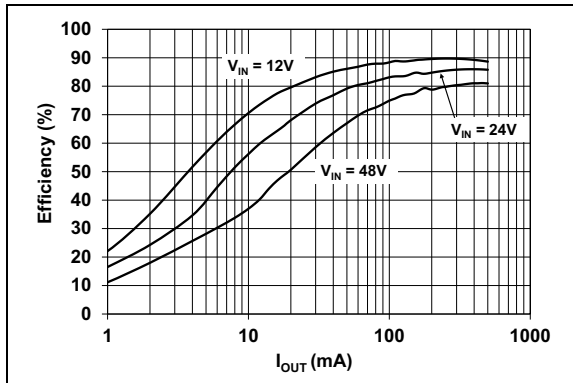


FIGURE 2-2: 5V V_{OUT} Efficiency vs. I_{OUT} .

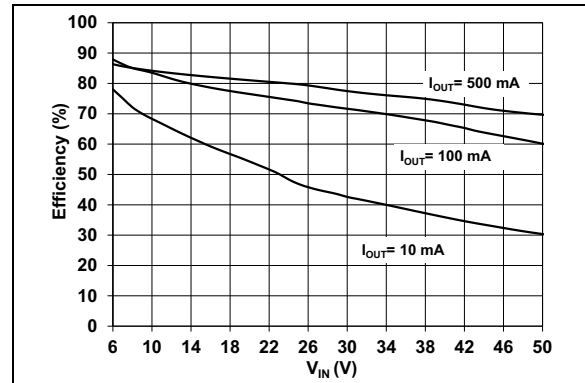


FIGURE 2-5: 3.3V V_{OUT} Efficiency vs. V_{IN} .

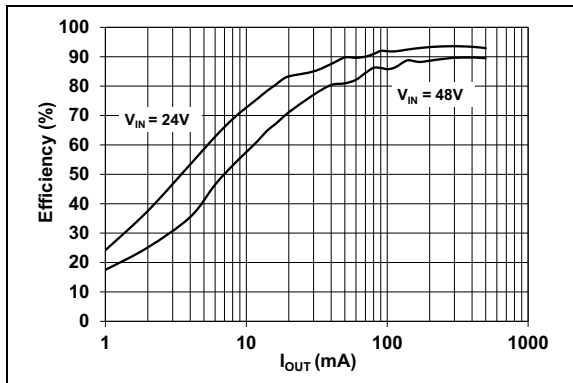


FIGURE 2-3: 12V V_{OUT} Efficiency vs. I_{OUT} .

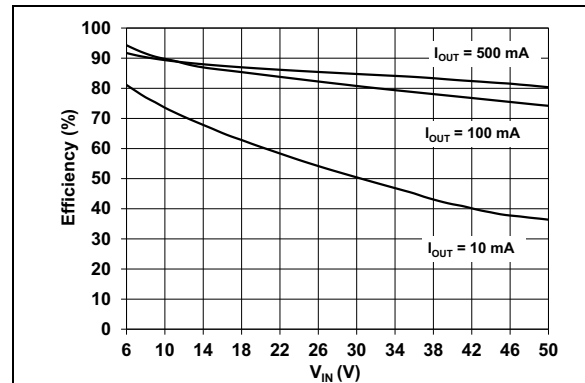


FIGURE 2-6: 5V V_{OUT} Efficiency vs. V_{IN} .

MCP16331

Note: Unless otherwise indicated, $V_{IN} = EN = 12V$, $C_{OUT} = C_{IN} = 2 \times 10 \mu F$, $L = 15 \mu H$, $V_{OUT} = 3.3V$, $I_{LOAD} = 100 \text{ mA}$, $T_A = +25^\circ C$, 6-Lead SOT-23 package.

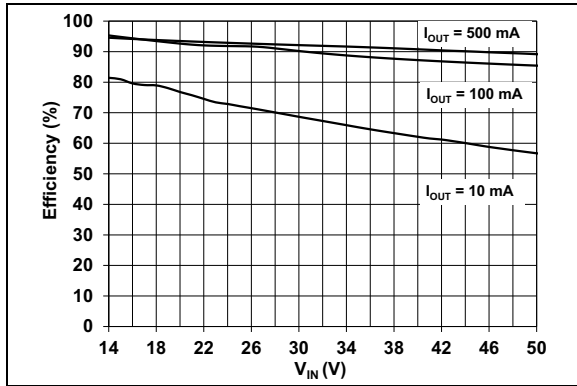


FIGURE 2-7: 12V V_{OUT} Efficiency vs. V_{IN} .

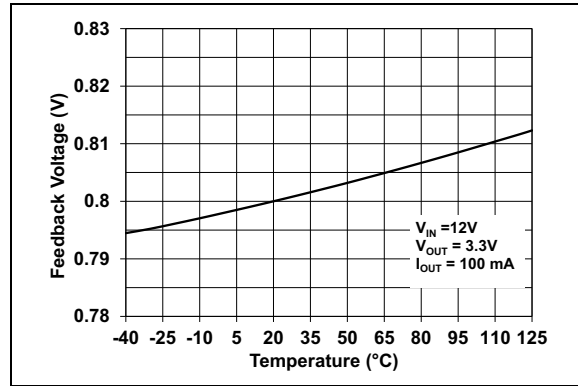


FIGURE 2-10: V_{FB} vs. Temperature.

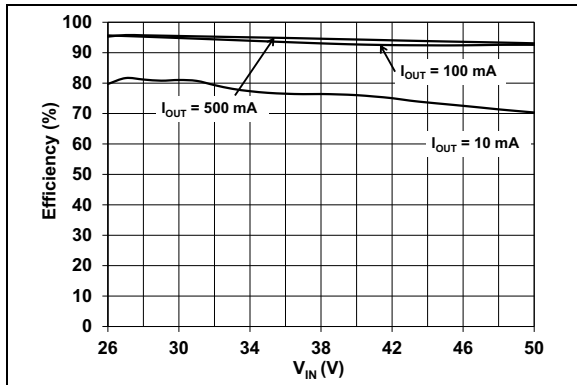


FIGURE 2-8: 24V V_{OUT} Efficiency vs. V_{IN} .

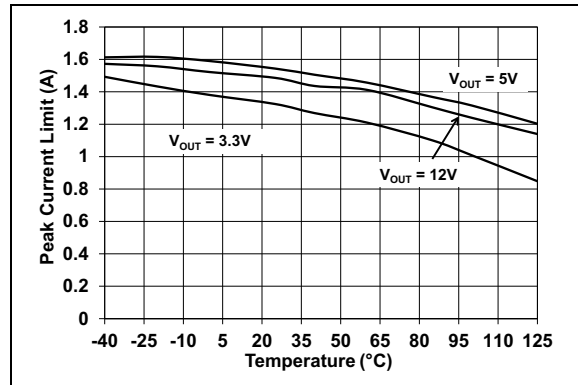


FIGURE 2-11: Peak Current Limit vs. Temperature.

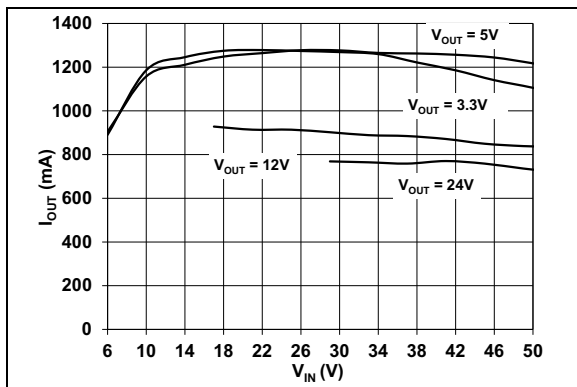


FIGURE 2-9: Max I_{OUT} vs. V_{IN} .

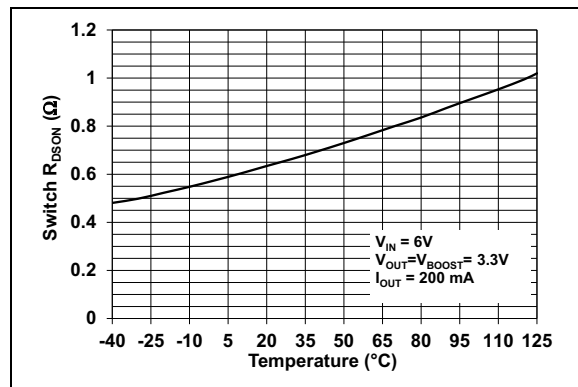


FIGURE 2-12: Switch $R_{DS(on)}$ vs. Temperature.

Note: Unless otherwise indicated, $V_{IN} = EN = 12V$, $C_{OUT} = C_{IN} = 2 \times 10 \mu F$, $L = 15 \mu H$, $V_{OUT} = 3.3V$, $I_{LOAD} = 100 \text{ mA}$, $T_A = +25^\circ C$, 6-Lead SOT-23 package.

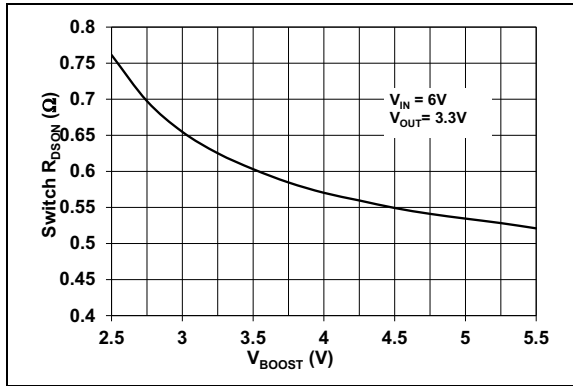


FIGURE 2-13: Switch $R_{DS(on)}$ vs. V_{BOOST} .

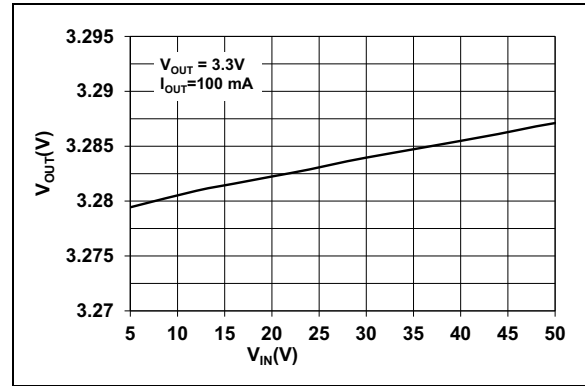


FIGURE 2-16: V_{OUT} vs V_{IN} .

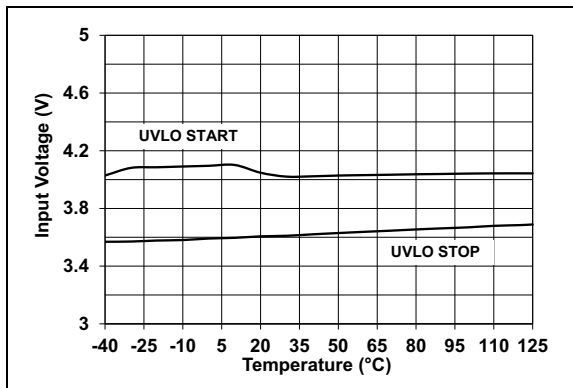


FIGURE 2-14: Undervoltage Lockout vs. Temperature.

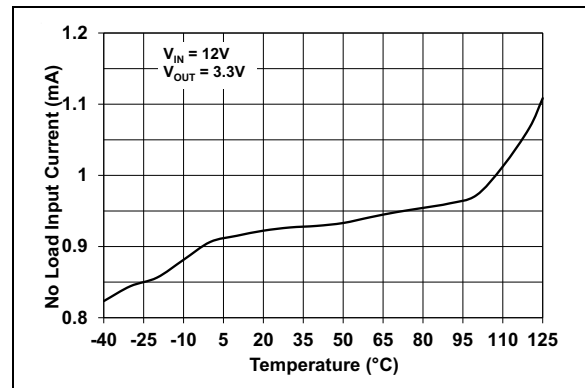


FIGURE 2-17: Input Quiescent Current vs. Temperature.

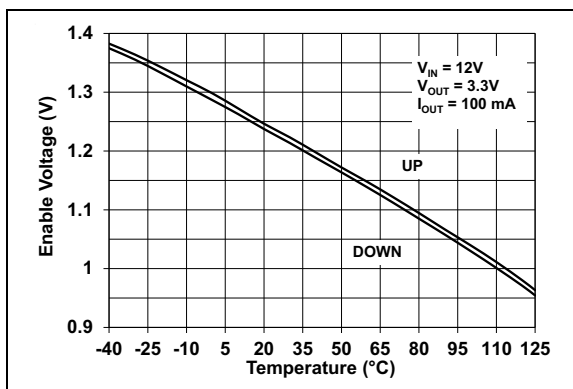


FIGURE 2-15: EN Threshold Voltage vs. Temperature.

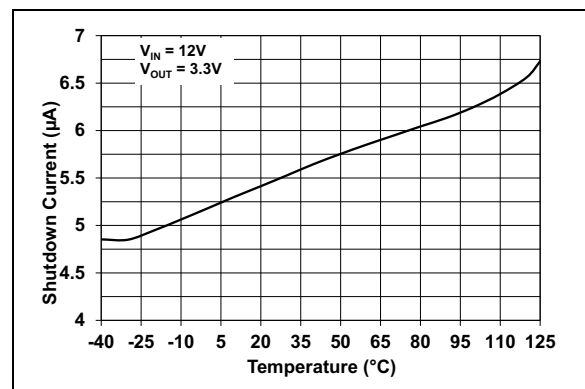


FIGURE 2-18: Shutdown Current vs. Temperature.

MCP16331

Note: Unless otherwise indicated, $V_{IN} = EN = 12V$, $C_{OUT} = C_{IN} = 2 \times 10 \mu F$, $L = 15 \mu H$, $V_{OUT} = 3.3V$, $I_{LOAD} = 100 \text{ mA}$, $T_A = +25^\circ C$, 6-Lead SOT-23 package.

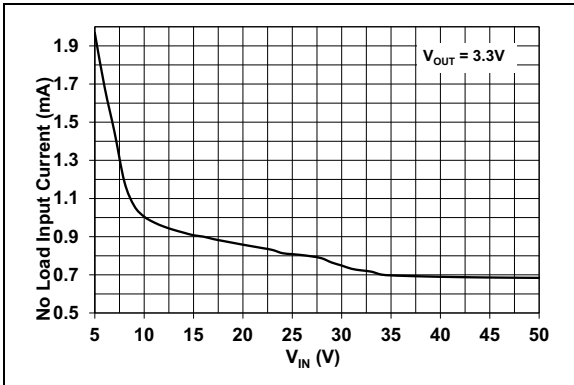


FIGURE 2-19: Input Quiescent Current vs. V_{IN} .

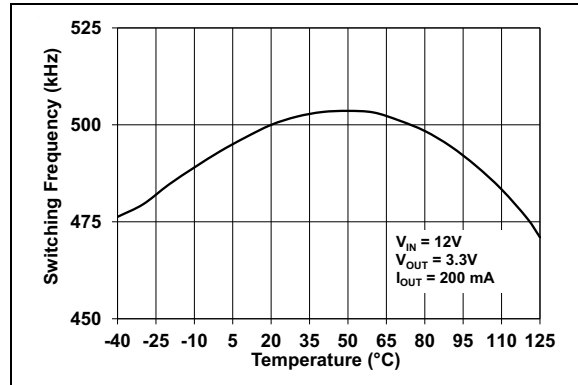


FIGURE 2-22: Switching Frequency vs. Temperature.

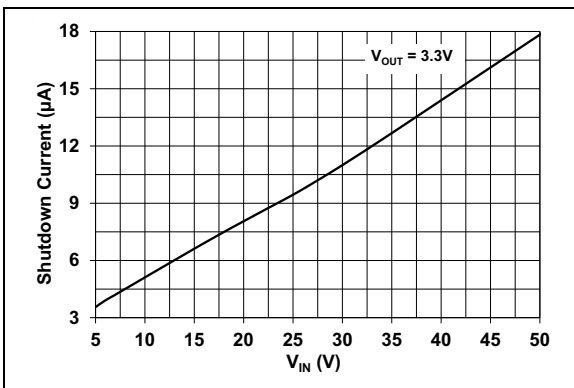


FIGURE 2-20: Shutdown Current vs. V_{IN} .

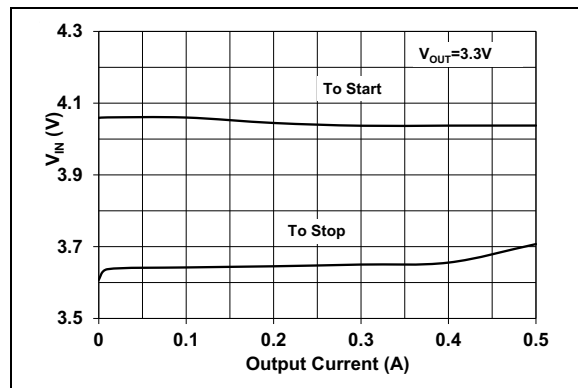


FIGURE 2-23: Minimum Input Voltage vs. Output Current.

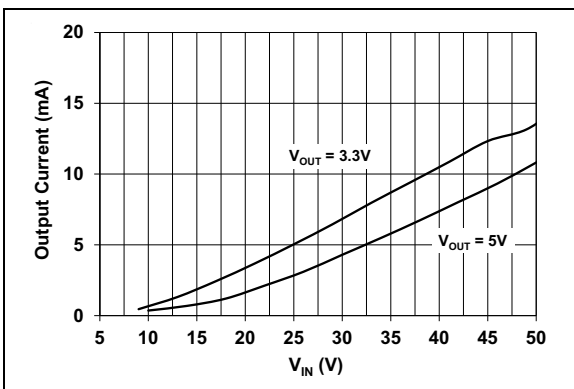


FIGURE 2-21: PWM/Skipping I_{OUT} Threshold vs. V_{IN} .

Note: Unless otherwise indicated, $V_{IN} = EN = 12V$, $C_{OUT} = C_{IN} = 2 \times 10 \mu F$, $L = 15 \mu H$, $V_{OUT} = 3.3V$, $I_{LOAD} = 100 \text{ mA}$, $T_A = +25^\circ C$, 6-Lead SOT-23 package.

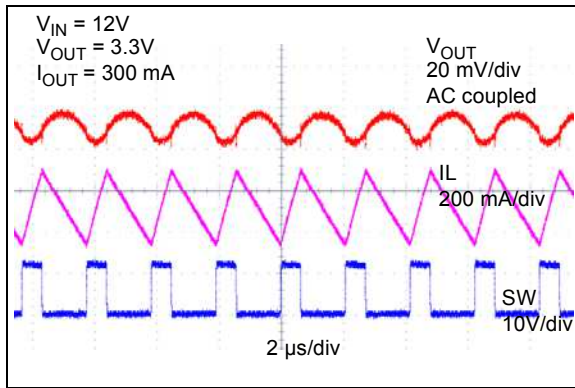


FIGURE 2-24: Heavy Load Switching Waveforms.

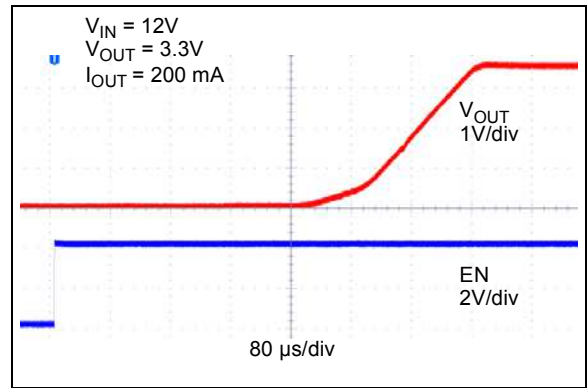


FIGURE 2-27: Startup from EN.

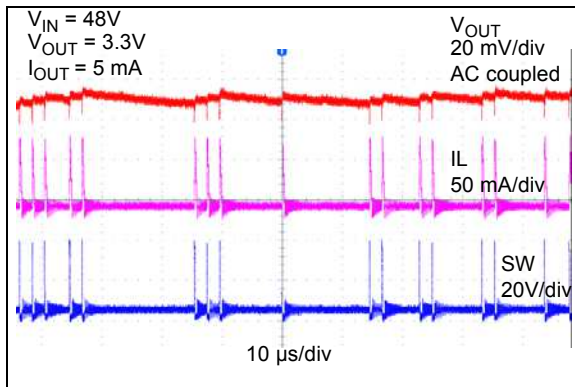


FIGURE 2-25: Light Load Switching Waveforms.

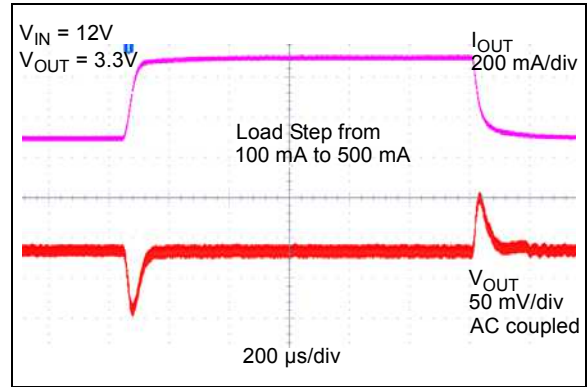


FIGURE 2-28: Load Transient Response.

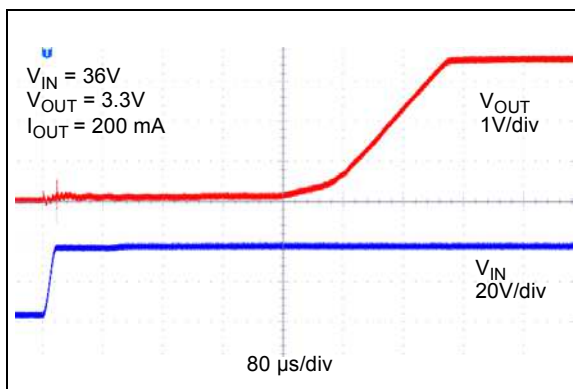


FIGURE 2-26: Startup from V_{IN} .

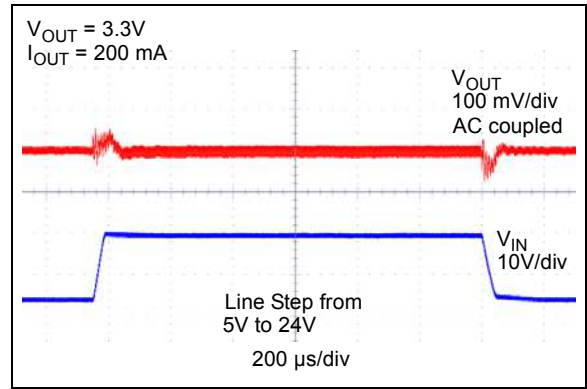


FIGURE 2-29: Line Transient Response.

MCP16331

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in [Table 3-1](#).

TABLE 3-1: PIN FUNCTION TABLE

MCP16331		Symbol	Description
TDFN	SOT-23		
1	6	SW	Output switch node, connects to the inductor, freewheeling diode and the bootstrap capacitor.
2	4	EN	Enable pin. There is an internal pull up on the V_{IN} . To turn the device off, connect EN to GND.
3	—	NC	Not connected
4	—	NC	Not connected
5	2	GND	Ground pin
6	3	V_{FB}	Output voltage feedback pin. Connect V_{FB} to an external resistor divider to set the output voltage.
7	1	BOOST	Boost voltage that drives the internal NMOS control switch. A bootstrap capacitor is connected between the BOOST and SW pins.
8	5	V_{IN}	Input supply voltage pin for power and internal biasing.
9	—	EP	Exposed Thermal Pad

3.1 Switch Node (SW)

The switch node pin is connected internally to the NMOS switch, and externally to the SW node consisting of the inductor and Schottky diode. The external Schottky diode should be connected close to the SW node and GND.

3.2 Enable Pin (EN)

The EN pin is a logic-level input used to enable or disable the device switching, and lower the quiescent current while disabled. By default the MCP16331 is enabled through an internal pull-up. To turn off the device, the EN pin must be pulled low.

3.3 Ground Pin (GND)

The ground or return pin is used for circuit ground connection. The length of the trace from the input cap return, output cap return and GND pin should be made as short as possible to minimize the noise on the GND pin.

3.4 Feedback Voltage Pin (V_{FB})

The V_{FB} pin is used to provide output voltage regulation by using a resistor divider. The V_{FB} voltage will be 0.8V typical with the output voltage in regulation.

3.5 Boost Pin (BOOST)

The supply for the floating high side driver used to turn the integrated N-Channel MOSFET on and off is connected to the boost pin.

3.6 Power Supply Input Voltage Pin (V_{IN})

Connect the input voltage source to V_{IN} . The input source should be decoupled to GND with a 4.7 μ F - 20 μ F capacitor, depending on the impedance of the source and output current. The input capacitor provides current for the switch node and a stable voltage source for the internal device power. This capacitor should be connected as close as possible to the V_{IN} and GND pins.

3.7 Exposed Thermal Pad Pin (EP)

There is an internal electrical connection between the EP and GND pin for the TDFN package.

NOTES:

MCP16331

4.0 DETAILED DESCRIPTION

4.1 Device Overview

The MCP16331 is a high input voltage step-down regulator, capable of supplying 500 mA to a regulated output voltage from 2.0V to 24V. Internally, the trimmed 500 kHz oscillator provides a fixed frequency, while the Peak Current Mode Control architecture varies the duty cycle for output voltage regulation. An internal floating driver is used to turn the high-side integrated N-Channel MOSFET on and off. The power for this driver is derived from an external boost capacitor (C_{BOOST}) whose energy is supplied from a fixed voltage ranging between 3.0V and 5.5V, typically the input or output voltage of the converter. For applications with an output voltage outside of this range, 12V for example, the boost capacitor bias can be derived from the output using a simple Zener diode regulator.

4.1.1 INTERNAL REFERENCE VOLTAGE V_{REF}

An integrated precise 0.8V reference combined with an external resistor divider sets the desired converter output voltage. The resistor divider range can vary without affecting the control system gain. High-value resistors consume less current, but are more susceptible to noise.

4.1.2 INTERNAL COMPENSATION

All control system components necessary for stable operation over the entire device operating range are integrated, including the error amplifier and inductor current slope compensation. To add the proper amount of slope compensation, the inductor value changes along with the output voltage (see [Table 5-1](#)).

4.1.3 EXTERNAL COMPONENTS

External components consist of:

- input capacitor
- output filter (inductor and capacitor)
- freewheeling diode
- boost capacitor
- boost blocking diode
- resistor divider

The selection of the external inductor, output capacitor, input capacitor and freewheeling diode is dependent upon the output voltage, input voltage and the maximum output current.

4.1.4 ENABLE INPUT

Enable input is used to disable the device, while connected to GND. If disabled, the MCP16331 device consumes a minimal current from the input.

4.1.5 SOFT START

The internal reference voltage rate of rise is controlled during startup, minimizing the output voltage overshoot and the inrush current.

4.1.6 UNDERVOLTAGE LOCKOUT

An integrated Undervoltage Lockout (UVLO) prevents the converter from starting until the input voltage is high enough for normal operation. The converter will typically start at 4.1V and operate down to 3.6V. Hysteresis is added to prevent starting and stopping during start-up as a result of loading the input voltage source.

4.1.7 OVERTEMPERATURE PROTECTION

Overtemperature protection limits the silicon die temperature to +160°C by turning the converter off. The normal switching resumes at +130°C.

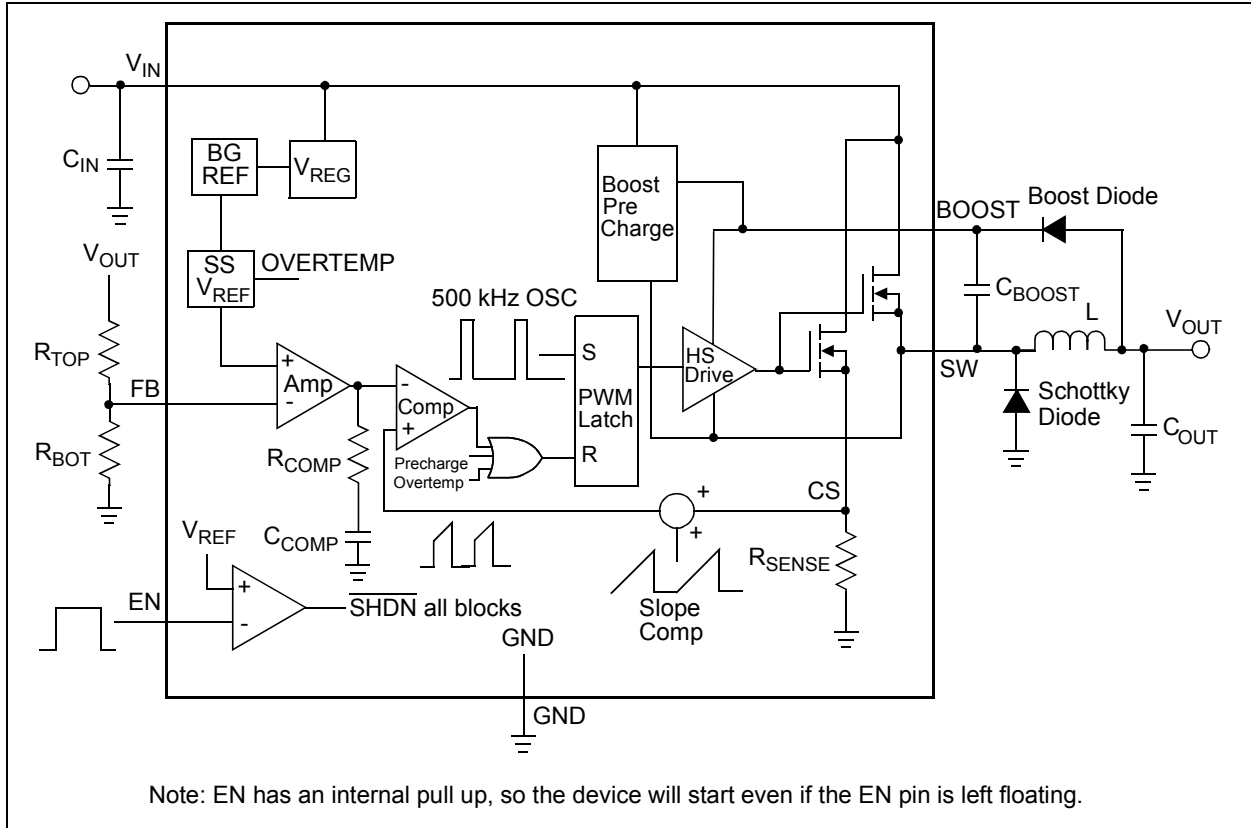


FIGURE 4-1: MCP16331 Block Diagram.

4.2 Functional Description

4.2.1 STEP-DOWN OR BUCK CONVERTER

The MCP16331 is a non-synchronous, step-down or buck converter capable of stepping input voltages ranging from 4.4V to 50V down to 2.0V to 24V for $V_{IN} > V_{OUT}$.

The integrated high side switch is used to chop or modulate the input voltage using a controlled duty cycle for output voltage regulation. High efficiency is achieved by using a low-resistance switch, low forward drop diode, low equivalent series resistance, inductor and capacitor. When the switch is turned on, a DC voltage is applied across the inductor ($V_{IN} - V_{OUT}$), resulting in a positive linear ramp of inductor current. When the switch turns off, the applied inductor voltage is equal to $-V_{OUT}$, resulting in a negative linear ramp of inductor current (ignoring the forward drop of the Schottky diode).

For steady-state, continuous inductor current operation, the positive inductor current ramp must equal the negative current ramp in magnitude. While operating in steady state, the switch duty cycle must be equal to the relationship of V_{OUT}/V_{IN} for constant output voltage regulation, under the condition that the inductor current is continuous, or never reaches zero. For discontinuous inductor current operation, the steady-state duty cycle will be less than V_{OUT}/V_{IN} to maintain voltage regulation. The average of the chopped input voltage or SW node voltage is equal to the output voltage, while the average of the inductor current is equal to the output current.

MCP16331

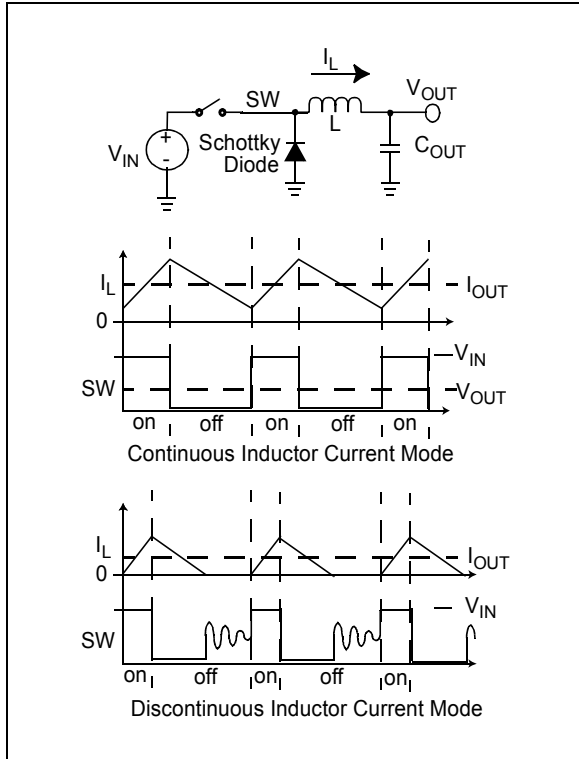


FIGURE 4-2: Step-Down Converter.

4.2.2 PEAK CURRENT MODE CONTROL

The MCP16331 integrates a Peak Current Mode Control architecture, resulting in superior AC regulation while minimizing the number of voltage loop compensation components and their size for integration. Peak Current Mode Control takes a small portion of the inductor current, replicates it and compares this replicated current sense signal with the output of the integrated error voltage. In practice, the inductor current and the internal switch current are equal during the switch-on time. By adding this peak current sense to the system control, the step-down power train system is reduced from a 2nd order to a 1st order. This reduces the system complexity and increases its dynamic performance.

For Pulse-Width Modulation (PWM) duty cycles that exceed 50%, the control system can become bimodal where a wide pulse followed by a short pulse repeats instead of the desired fixed-pulse width. To prevent this mode of operation, an internal compensating ramp is summed into the current shown in [Figure 4-2](#).

4.2.3 PULSE-WIDTH MODULATION (PWM)

The internal oscillator periodically starts the switching period, which in MCP16331's case occurs every 2 μ s or 500 kHz. With the integrated switch turned on, the inductor current ramps up until the sum of the current sense and slope compensation ramp exceeds the integrated error amplifier output. The error amplifier output slews up or down to increase or decrease the inductor peak current feeding into the output LC filter. If the regulated output voltage is lower than its target, the error amplifier output rises. This results in an increase in the inductor current to correct for error in the output voltage. The fixed frequency duty cycle is terminated when the sensed inductor peak current summed with the internal slope compensation exceeds the output voltage of the error amplifier. The PWM latch is set by turning off the internal switch and preventing it from turning on until the beginning of the next cycle. An overtemperature signal or boost cap undervoltage can also reset the PWM latch to terminate the cycle.

When working close to the boundary conduction threshold, a jitter on the SW node may occur, reflecting in the output voltage. Although the low-frequency output component is very small, it may be desirable to completely eliminate this component. To achieve this, different methods can be applied to reduce or completely eliminate this component. In addition to a very good layout, a capacitor in parallel with the top feedback resistor or an RC snubber between the SW node and GND can be added.

Typical values for the snubber are 680 pF and 430 Ω , while the capacitor in parallel with the top feedback resistor can use values from 10 pF to 47 pF. Using such a snubber eliminates the ringing on the SW node, but decreases the overall efficiency of the converter.

4.2.4 HIGH SIDE DRIVE

The MCP16331 features an integrated high-side N-Channel MOSFET for high-efficiency step-down power conversion. An N-Channel MOSFET is used for its low resistance and size (instead of a P-Channel MOSFET). A gate drive voltage above the input is necessary to turn on the high side N-Channel. The high side drive voltage should be between 3.0V and 5.5V. The N-Channel source is connected to the inductor and Schottky diode, or switch node. When the switch is off, the boost cap voltage is replenished, typically from the output voltage for 3V to 5V output applications. A boost-blocking diode is used to prevent current flow from the boost cap back into the output during the internal switch-on time.

Prior to startup, the boost cap has no stored charge to drive the switch. An internal regulator is used to “precharge” the boost cap. Once precharged, the switch is turned on and the inductor current flows. When the switch turns off, the inductor current free-wheels through the Schottky diode, providing a path to recharge the boost cap. Worst-case conditions for recharge occur when the switch turns on for a very short duty cycle at light load, limiting the inductor current ramp. In this case, there is a small amount of time for the boost capacitor to recharge. For high input voltages there is enough precharge current to replace the boost cap charge. For input voltages above 5.5V typical, the MCP16331 device will regulate the output voltage with no load. After starting, the MCP16331 will regulate the output voltage until the input voltage decreases below 4V. See [Figure 2-23](#) for device range of operation over input voltage, output voltage and load.

4.2.5 ALTERNATIVE BOOST BIAS

For 3.0V to 5.0V output voltage applications, the boost supply is typically the output voltage. For applications with $V_{OUT} < 3.0V$ or $V_{OUT} > 5.0V$, an alternative boost supply can be used.

Alternative boost supplies can be from the input, input derived, output derived or an auxiliary system voltage.

For low-voltage output applications with unregulated input voltage, a shunt regulator derived from the input can be used to derive the boost supply. For applications with high-output voltage or regulated high-input voltage, a series regulator can be used to derive the boost supply. In case the boost is biased from an external source while in shutdown, the device will draw slightly higher current.

MCP16331

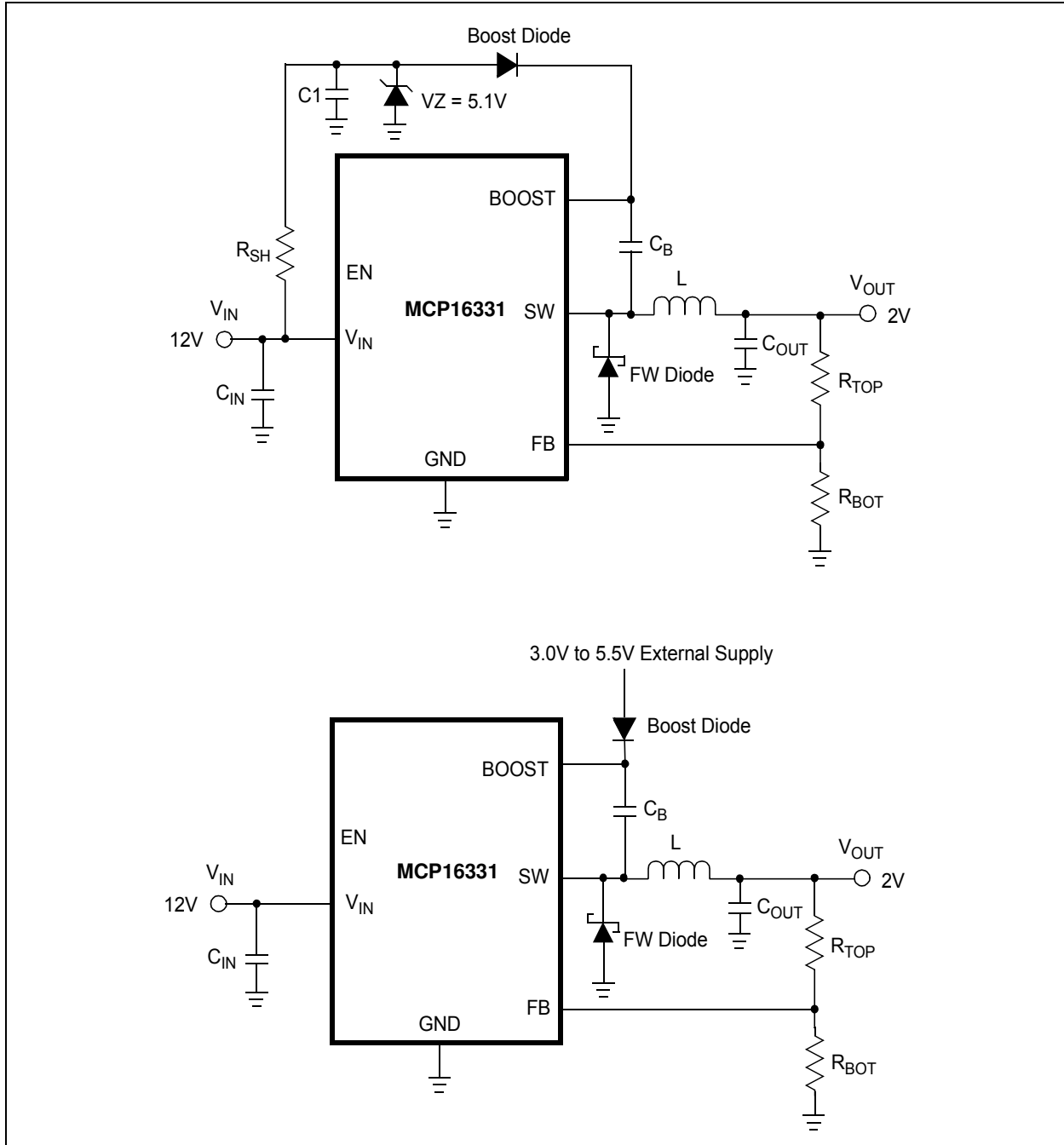


FIGURE 4-3: Shunt and External Boost Supply.

Shunt Boost Supply Regulation is used for low-output voltage converters operating from a wide ranging input source. A regulated 3.0V to 5.5V supply is needed to provide high-side drive bias. The shunt uses a Zener diode to clamp the voltage within the 3.0V to 5.5V range using the resistance shown in [Figure 4-3](#).

To calculate the shunt resistance, the boost drive current can be estimated using [Equation 4-1](#).

I_{BOOST_TYP} for 3.3V Boost Supply = 0.6 mA

I_{BOOST_TYP} for 5.0V Boost Supply = 0.8 mA.

EQUATION 4-1: BOOST CURRENT

$$I_{BOOST} = I_{BOOST_TYP} \times 1.5mA$$

To calculate the shunt resistance, the maximum I_{BOOST} and I_Z current are used at the minimum input voltage (Equation 4-2).

V_Z and I_Z can be found on the Zener diode manufacturer's data sheet. Typically, $I_Z = 1 \text{ mA}$.

EQUATION 4-2: SHUNT RESISTANCE

$$R_{SH} = \frac{V_{INMIN} - V_Z}{I_{Boost} + I_Z}$$

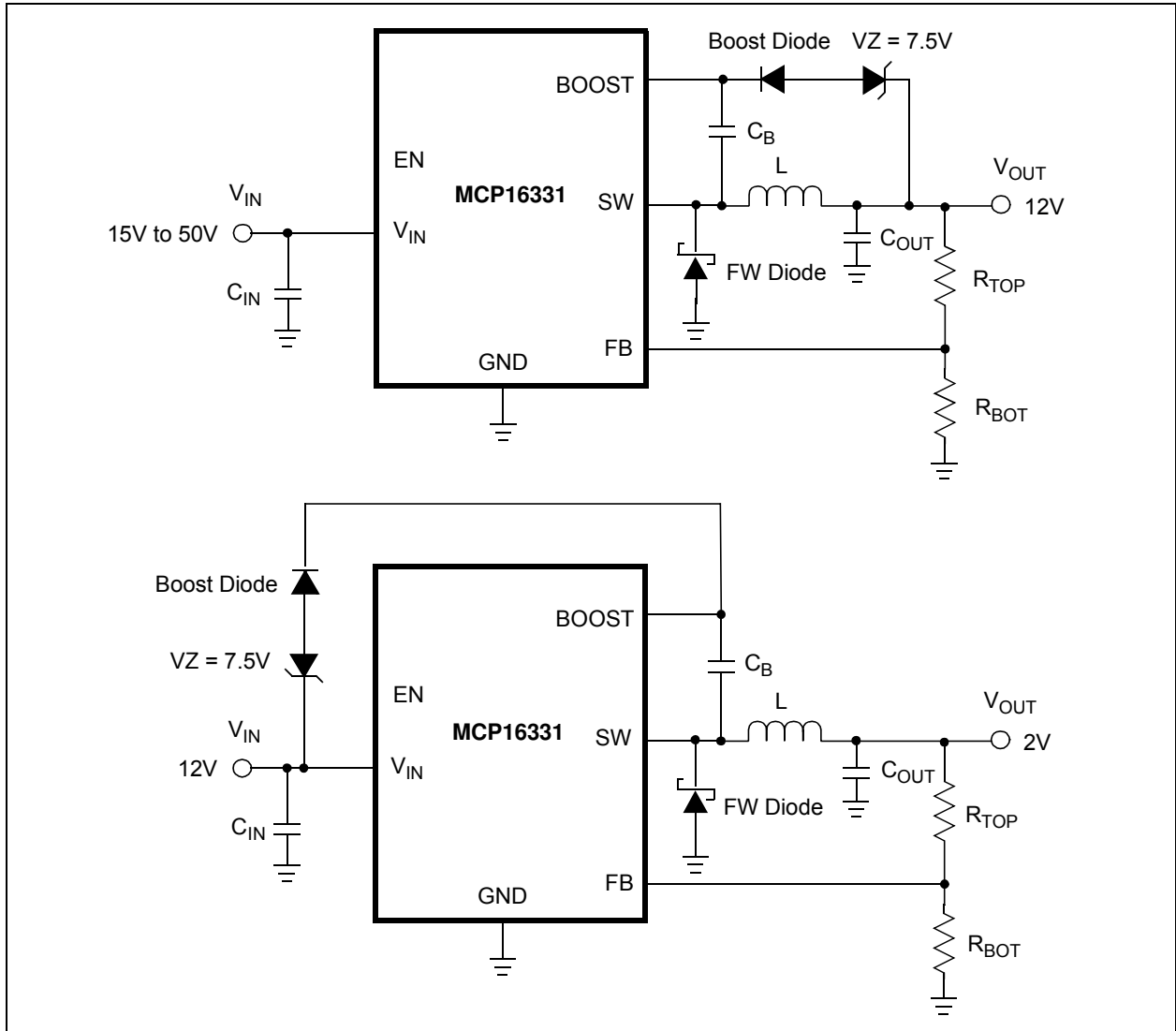


FIGURE 4-4: Series Regulator Boost Supply.

Series regulator applications use a Zener diode to drop the excess voltage. The series regulator bias source can be input or output voltage derived, as shown in Figure 4-4. The boost supply must remain between 3.0V and 5.5V at all times for proper circuit operation.

MCP16331

5.0 APPLICATION INFORMATION

5.1 Typical Applications

The MCP16331 step-down converter operates over a wide input voltage range, up to 50V maximum. Typical applications include generating a bias or V_{DD} voltage for the PIC[®] microcontroller product line, digital control system bias supply for AC-DC converters, 24V industrial input and similar applications.

5.2 Adjustable Output Voltage Calculations

To calculate the resistor divider values for the MCP16331, Equation 5-1 can be used. R_{TOP} is connected to V_{OUT} . R_{BOT} is connected to GND and both are connected to the V_{FB} input pin.

EQUATION 5-1:

$$R_{TOP} = R_{BOT} \times \left(\frac{V_{OUT}}{V_{FB}} - 1 \right)$$

EXAMPLE 5-1:

$$\begin{aligned} V_{OUT} &= 3.3V \\ V_{FB} &= 0.8V \\ R_{BOT} &= 10 \text{ k}\Omega \\ R_{TOP} &= 31.25 \text{ k}\Omega \text{ (standard value = 31.6 k}\Omega\text{)} \\ V_{OUT} &= 3.328V \text{ (using standard value)} \end{aligned}$$

EXAMPLE 5-2:

$$\begin{aligned} V_{OUT} &= 5.0V \\ V_{FB} &= 0.8V \\ R_{BOT} &= 10 \text{ k}\Omega \\ R_{TOP} &= 52.5 \text{ k}\Omega \text{ (standard value = 52.3 k}\Omega\text{)} \\ V_{OUT} &= 4.98V \text{ (using standard value)} \end{aligned}$$

The transconductance error amplifier gain is controlled by its internal impedance. The external divider resistors have no effect on system gain so a wide range of values can be used. A 10 k Ω resistor is recommended as a good trade-off for quiescent current and noise immunity.

5.3 General Design Equations

The step-down converter duty cycle can be estimated using Equation 5-2, while operating in Continuous Inductor Current Mode. This equation also counts the forward drop of the freewheeling diode and internal N-Channel MOSFET switch voltage drop. As the load current increases, the switch voltage drop and diode voltage drop increase, requiring a larger PWM duty cycle to maintain the output voltage regulation. Switch voltage drop is estimated by multiplying the switch current times the switch resistance or $R_{DS(ON)}$.

EQUATION 5-2: CONTINUOUS INDUCTOR CURRENT DUTY CYCLE

$$D = \frac{(V_{OUT} + V_{Diode})}{(V_{IN} - (I_{SW} \times R_{DS(ON)})}$$

The MCP16331 device features an integrated slope compensation to prevent the bimodal operation of the PWM duty cycle. Internally, half of the inductor current down slope is summed with the internal current sense signal. For the proper amount of slope compensation, it is recommended to keep the inductor down-slope current constant by varying the inductance with V_{OUT} , where $K = 0.22V/\mu H$.

EQUATION 5-3:

$$K = V_{OUT}/L$$

TABLE 5-1: RECOMMENDED INDUCTOR VALUES

V_{OUT}	K	$L_{STANDARD}$
2.0V	0.20	10 μH
3.3V	0.22	15 μH
5.0V	0.23	22 μH
12V	0.21	56 μH
15V	0.22	68 μH
24V	0.24	100 μH

5.4 Input Capacitor Selection

The step-down converter input capacitor must filter the high-input ripple current, as a result of pulsing or chopping the input voltage. The MCP16331 input voltage pin is used to supply voltage for the power train and as a source for internal bias. A low Equivalent Series Resistance (ESR), preferably a ceramic capacitor, is recommended. The necessary capacitance is dependent upon the maximum load current and source impedance. Three capacitor parameters to keep in mind are the voltage rating, equivalent series resistance and the temperature rating. For wide temperature-range applications, a multi-layer X7R dielectric is mandatory, while for applications with limited temperature range, a multi-layer X5R dielectric is acceptable. Typically, input capacitance between 4.7 μF and 20 μF is sufficient for most applications.

The input capacitor voltage rating should be a minimum of V_{IN} plus margin. Table 5-2 contains the recommended range for the input capacitor value.

5.5 Output Capacitor Selection

The output capacitor helps in providing a stable output voltage during sudden load transients, and reduces the output voltage ripple. As with the input capacitor, X5R and X7R ceramic capacitors are well suited for this application.

The amount and type of output capacitance and equivalent series resistance will have a significant effect on the output ripple voltage and system stability. The range of the output capacitance is limited due to the integrated compensation of the MCP16331.

The output voltage capacitor voltage rating should be a minimum of V_{OUT} , plus margin.

Table 5-2 contains the recommended range for the input and output capacitor value:

TABLE 5-2: CAPACITOR VALUE RANGE

Parameter	Min.	Max.
C_{IN}	4.7 μF	none
C_{OUT}	20 μF	—

5.6 Inductor Selection

The MCP16331 is designed to be used with small surface mount inductors. Several specifications should be considered prior to selecting an inductor. To optimize system performance, the inductance value is determined by the output voltage (Table 5-1) so the inductor ripple current is somewhat constant over the output voltage range.

EQUATION 5-4: INDUCTOR RIPPLE CURRENT

$$\Delta I_L = \frac{V_{IN} - V_{OUT}}{L} \times t_{ON}$$

EXAMPLE 5-3:

$$\begin{aligned} V_{IN} &= 12\text{V} \\ V_{OUT} &= 3.3\text{V} \\ I_{OUT} &= 500\text{ mA} \end{aligned}$$

EQUATION 5-5: INDUCTOR PEAK CURRENT

$$I_{LPK} = \frac{\Delta I_L}{2} + I_{OUT}$$

$$\begin{aligned} \text{Inductor ripple current} &= 319\text{ mA} \\ \text{Inductor peak current} &= 660\text{ mA} \end{aligned}$$

For the example above, an inductor saturation rating of minimum 660 mA is recommended. Low DCR inductors result in higher system efficiency. A trade-off between size, cost and efficiency is made to achieve the desired results.

MCP16331

TABLE 5-3: MCP16331 RECOMMENDED 3.3V INDUCTORS

Part Number	Value (μH)	DCR (Ω)	I _{SAT} (A)	Size WxLxH (mm)
Coilcraft®				
ME3220-153	15	0.52	0.90	3.2x2.5x2.0
LPS4414-153	15	0.440	0.92	4.4x4.4x1.4
LPS6235-153	15	0.125	2.00	6.2x6.2x3.5
MSS6132-153	15	0.106	1.56	6.1x6.1x3.2
MSS7341-153	15	0.055	1.78	6.6x6.6x4.1
LPS3015-153	15	0.700	0.62	3.0x3.0x1.5
Würth Elektronik®				
744025150	15	0.400	0.900	2.8x2.8x2.8
744042150	15	0.22	0.75	4.8x4.8x1.8
7447779115	15	0.081	2.2	7.3x7.3x4.5
Coiltronics®				
SD12-150R	15	0.408	0.692	5.2x5.2x1.2
SD3118-150-R	15	0.44	0.75	3.2x3.2x1.8
SD52-150-R	15	0.161	0.88	5.2x5.5x2.0
Sumida®				
CDPH4D19FNP-150MC	15	0.075	0.66	5.2x5.2x2.0
CDRH3D16/HPNP-150MC	15	0.410	0.65	4.0x4.0x1.8
TDK - EPCOS®				
B82462G4153M	15	0.097	1.05	6.3x6.3x3

TABLE 5-4: MCP16331 RECOMMENDED 5V INDUCTORS

Part Number	Value (μH)	DCR (Ω)	I _{SAT} (A)	Size WxLxH (mm)
Coilcraft®				
ME3220-223	22	0.787	0.71	3.2x2.5x2.0
LPS4414-223	22	0.59	0.74	4.4x4.4x1.4
LPS6235-223	22	0.145	1.7	6.2x6.2x3.5
MSS6132-223	22	0.158	1.22	6.1x6.1x3.2
MSS7341-223	22	0.082	1.42	6.6x6.6x4.1
LPS3015-223	22	0.825	0.5	3.0x3.0x1.5
Würth Elektronik®				
744025220	22	0.575	0.75	2.8x2.8x2.8
744042220	22	0.3	0.6	4.8x4.8x1.8
7447779122	22	0.11	1.7	7.3x7.3x4.5
Cooper Bussman®				
SD12-220-R	22	0.633	0.574	5.2x5.2x1.2
SD3118-220-R	22	0.676	0.61	3.2x3.2x1.8
SD52-220-R	22	0.204	0.73	5.2x5.2x2
Sumida®				
CDPH4D19FNP-220MC	22	0.135	0.54	5.2x5.2x2
CDRH3D16/HPNP-220MC	22	0.61	0.55	4.0x4.0x1.8
TDK - EPCOS®				
82462G4223M	22	0.15	0.85	6.3x6.3x3

5.7 Freewheeling Diode

The freewheeling diode creates a path for inductor current flow after the internal switch is turned off. The average diode current is dependent upon output load current at duty cycle (D). The efficiency of the converter is a function of the forward drop and speed of the freewheeling diode. A low forward drop Schottky diode is recommended. The current rating and voltage rating of the diode is application dependent. The diode voltage rating should be a minimum of V_{IN} , plus margin. The average diode current can be calculated using [Equation 5-6](#).

EQUATION 5-6: DIODE AVERAGE CURRENT

$$I_{DAVG} = (1 - D) \times I_{OUT}$$

EXAMPLE 5-4:

I_{OUT}	=	0.5A
V_{IN}	=	15V
V_{OUT}	=	5V
D	=	5/15
I_{DAVG}	=	333 mA

A 0.5A to 1A Diode is recommended.

TABLE 5-5: FREEWHEELING DIODES

App	Manufacturer	Part Number	Rating
12 V_{IN} 500 mA	Diodes Inc.	DFLS120L-7	20V, 1A
24 V_{IN} 100 mA	Diodes Inc.	B0540Ws-7	40V, 0.5A
18 V_{IN} 500 mA	Diodes Inc.	B130L-13-F	30V, 1A
48 V_{IN} 500 mA	Diodes Inc.	B1100	100V, 1A

5.8 Boost Diode

The boost diode is used to provide a charging path from the low-voltage gate drive source while the switch node is low. The boost diode blocks the high voltage of the switch node from feeding back into the output voltage when the switch is turned on, forcing the switch node high.

A standard 1N4148 ultra-fast diode is recommended for its recovery speed, high voltage blocking capability, availability and cost. The voltage rating required for the boost diode is V_{IN} .

For low-boost voltage applications, a small Schottky diode with the appropriately rated voltage can be used to lower the forward drop increasing the boost supply for gate drive.

5.9 Boost Capacitor

The boost capacitor is used to supply current for the internal high side drive circuitry that is above the input voltage. The boost capacitor must store enough energy to completely drive the high-side switch on and off. A 0.1 μ F X5R or X7R capacitor is recommended for all applications. The boost capacitor maximum voltage is 5.5V, so a 6.3V or 10V rated capacitor is recommended.

5.10 Thermal Calculations

The MCP16331 is available in 6-lead SOT-23 and 8-lead TDFN packages. By calculating the power dissipation and applying the package thermal resistance (θ_{JA}), the junction temperature is estimated.

To quickly estimate the internal power dissipation for the switching step-down regulator, an empirical calculation using measured efficiency can be used. Given

the measured efficiency, the internal power dissipation is estimated by Equation 5-7. This power dissipation includes all internal and external component losses. For a quick internal estimate, subtract the estimated Schottky diode loss and inductor DCR loss from the P_{DIS} calculation in Equation 5-7.

EQUATION 5-7: TOTAL POWER DISSIPATION ESTIMATE

$$\left(\frac{V_{OUT} \times I_{OUT}}{\text{Efficiency}} \right) - (V_{OUT} \times I_{OUT}) = P_{Dis}$$

The difference between the first term, input power, and the second term, power delivered, is the total system power dissipation. The freewheeling Schottky diode losses are determined by calculating the average diode current and multiplying by the diode forward drop. The inductor losses are estimated by $P_L = I_{OUT}^2 \times L_{DCR}$.

EQUATION 5-8: DIODE POWER DISSIPATION ESTIMATE

$$P_{Diode} = V_F \times ((1 - D) \times I_{OUT})$$

EXAMPLE 5-5:

V_{IN}	=	10V
V_{OUT}	=	5.0V
I_{OUT}	=	0.4A
Efficiency	=	90%
Total System Dissipation	=	222 mW
L_{DCR}	=	0.15 Ω
P_L	=	24 mW
Diode V_F	=	0.50
D	=	50%
P_{Diode}	=	125 mW

MCP16331 internal power dissipation estimate:

$$P_{DIS} - P_L - P_{DIODE} = 73 \text{ mW}$$

θ_{JA}	=	198°C/W
Estimated Junction Temperature Rise	=	+14.5°C

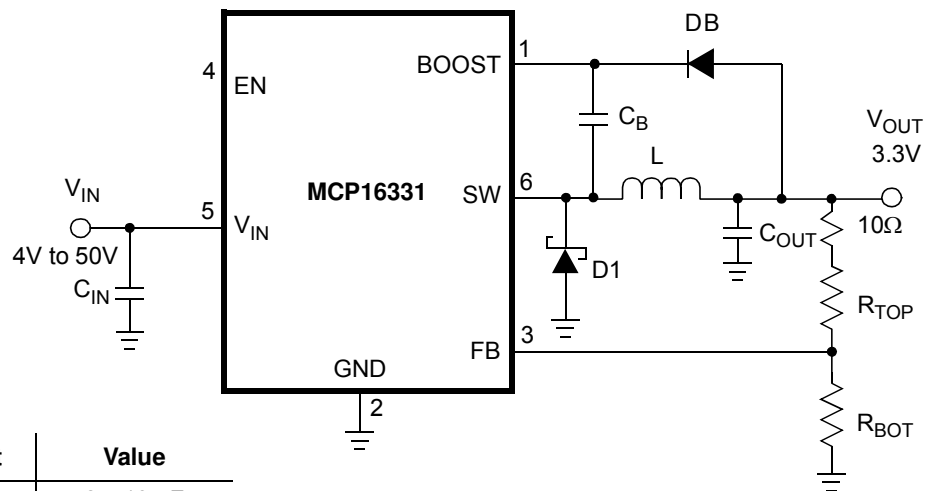
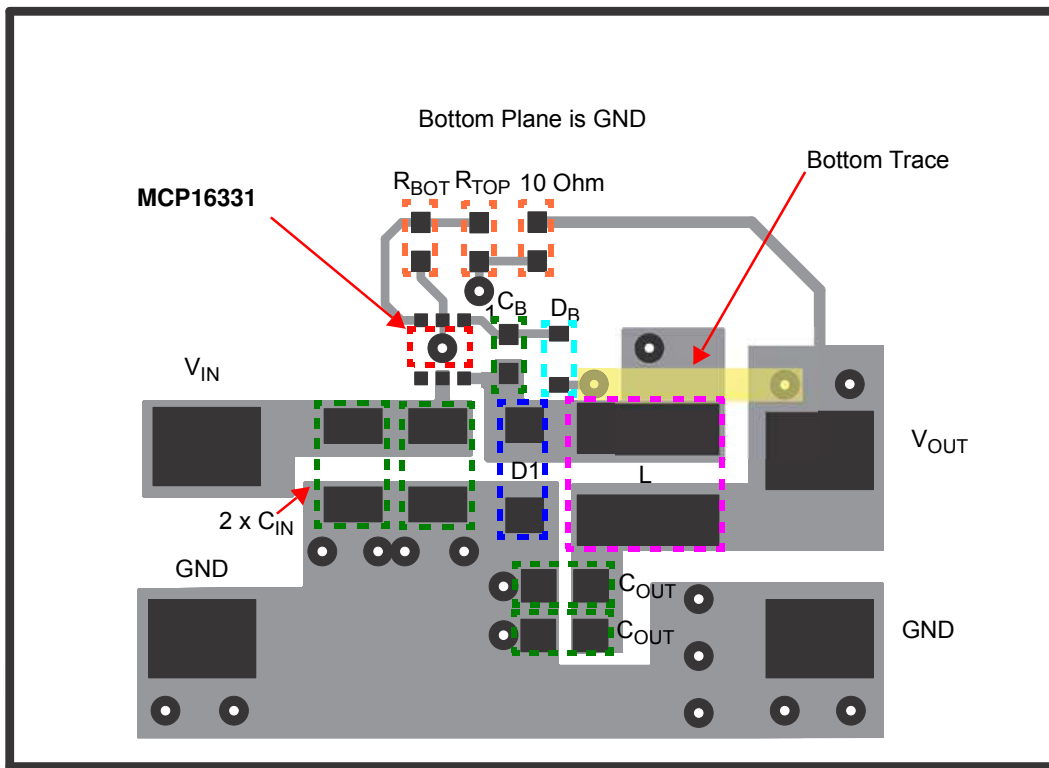
MCP16331

5.11 PCB Layout Information

Good printed circuit board layout techniques are important to any switching circuitry, and switching power supplies are no different. When wiring the switching high-current paths, short and wide traces should be used. Therefore, it is important that the input and output capacitors be placed as close as possible to the MCP16331 to minimize the loop area.

The feedback resistors and feedback signal should be routed away from the switching node and the switching current loop. When possible, ground planes and traces should be used to help shield the feedback signal and minimize noise and magnetic interference.

A good MCP16331 layout starts with C_{IN} placement. C_{IN} supplies current to the input of the circuit when the switch is turned on. In addition to supplying high-frequency switch current, C_{IN} also provides a stable voltage source for the internal MCP16331 circuitry. Unstable PWM operation can result if there are excessive transients or ringing on the V_{IN} pin of the MCP16331 device. In [Figure 5-1](#), C_{IN} is placed close to pin 5. A ground plane on the bottom of the board provides a low resistive and inductive path for the return current. The next priority in placement is the freewheeling current loop formed by D1, C_{OUT} and L, while strategically placing C_{OUT} return close to C_{IN} return. Next, the boost capacitor should be placed between the boost pin and the switch node pin SW. This leaves space close to the MCP16331 V_{FB} pin to place R_{TOP} and R_{BOT} . R_{TOP} and R_{BOT} are routed away from the Switch node so noise is not coupled into the high-impedance V_{FB} input.



Component	Value
C_{IN}	2 x 10 μ F
C_{OUT}	2 x 10 μ F
L	15 μ H
R_{TOP}	31.2 k Ω
R_{BOT}	10 k Ω
D1	B1100
D _B	1N4148
C_B	100 nF

***Note:** A 10 Ω resistor is used with network analyzer, to measure system gain and phase.

FIGURE 5-1: MCP16331 SOT-23-6 Recommended Layout, 500 mA Design.

MCP16331

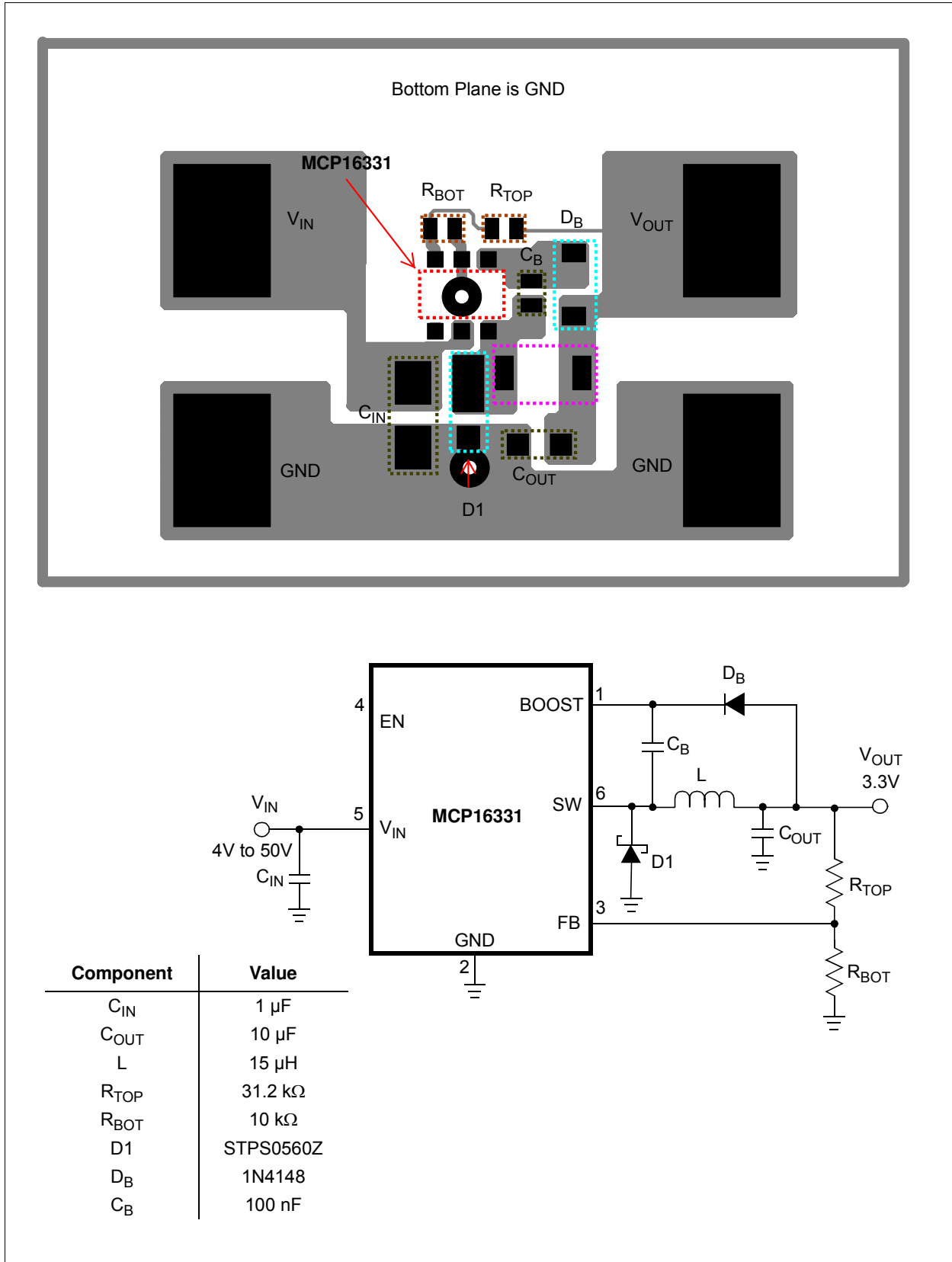


FIGURE 5-2: Compact MCP16331 SOT-23-6 D^2 Recommended Layout, Low Current Design.

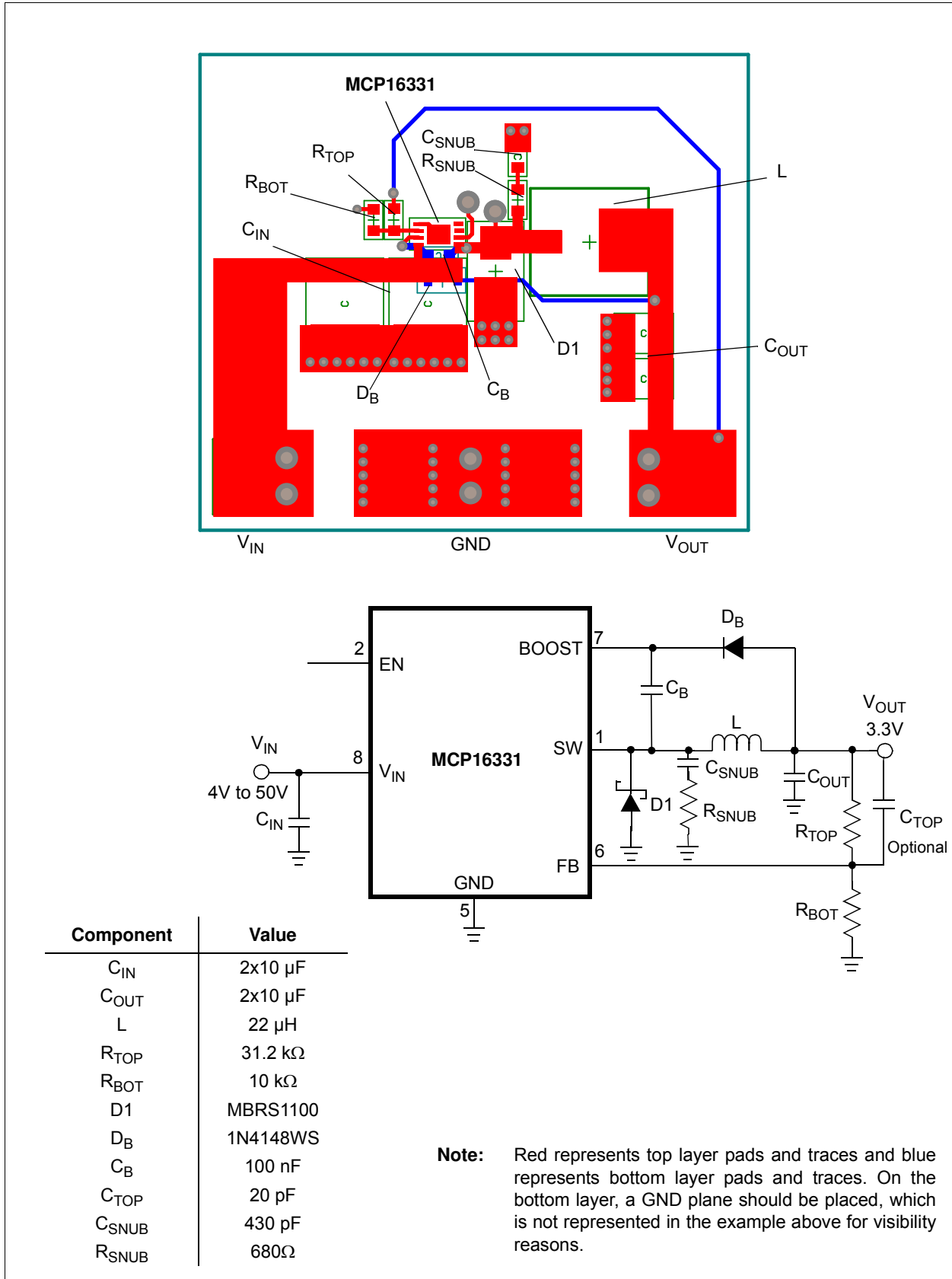


FIGURE 5-3: MCP16331 TDFN-8 Recommended Layout Design.

MCP16331

6.0 TYPICAL APPLICATION CIRCUITS

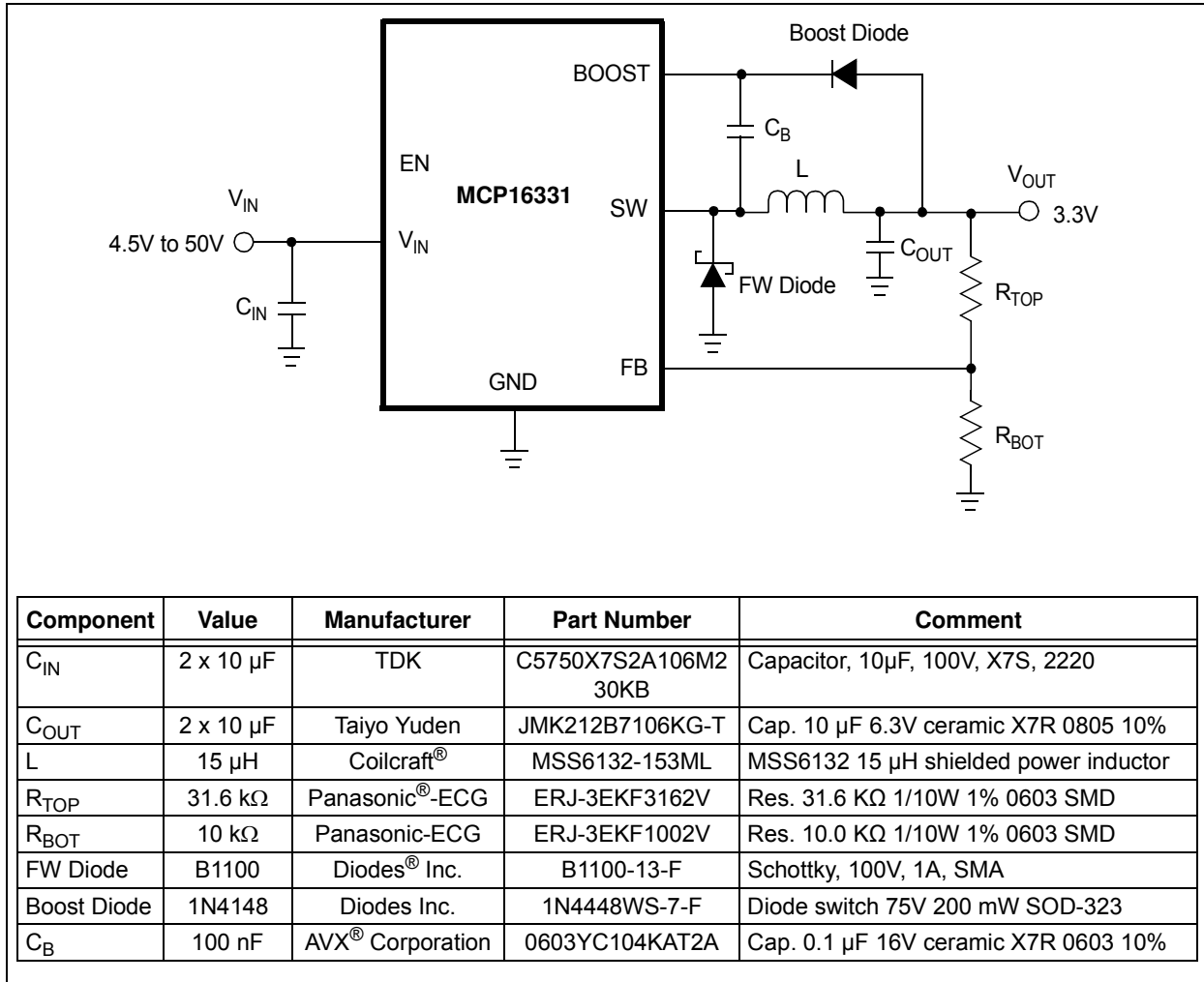


FIGURE 6-1: Typical Application 50V V_{IN} to 3.3V V_{OUT} .

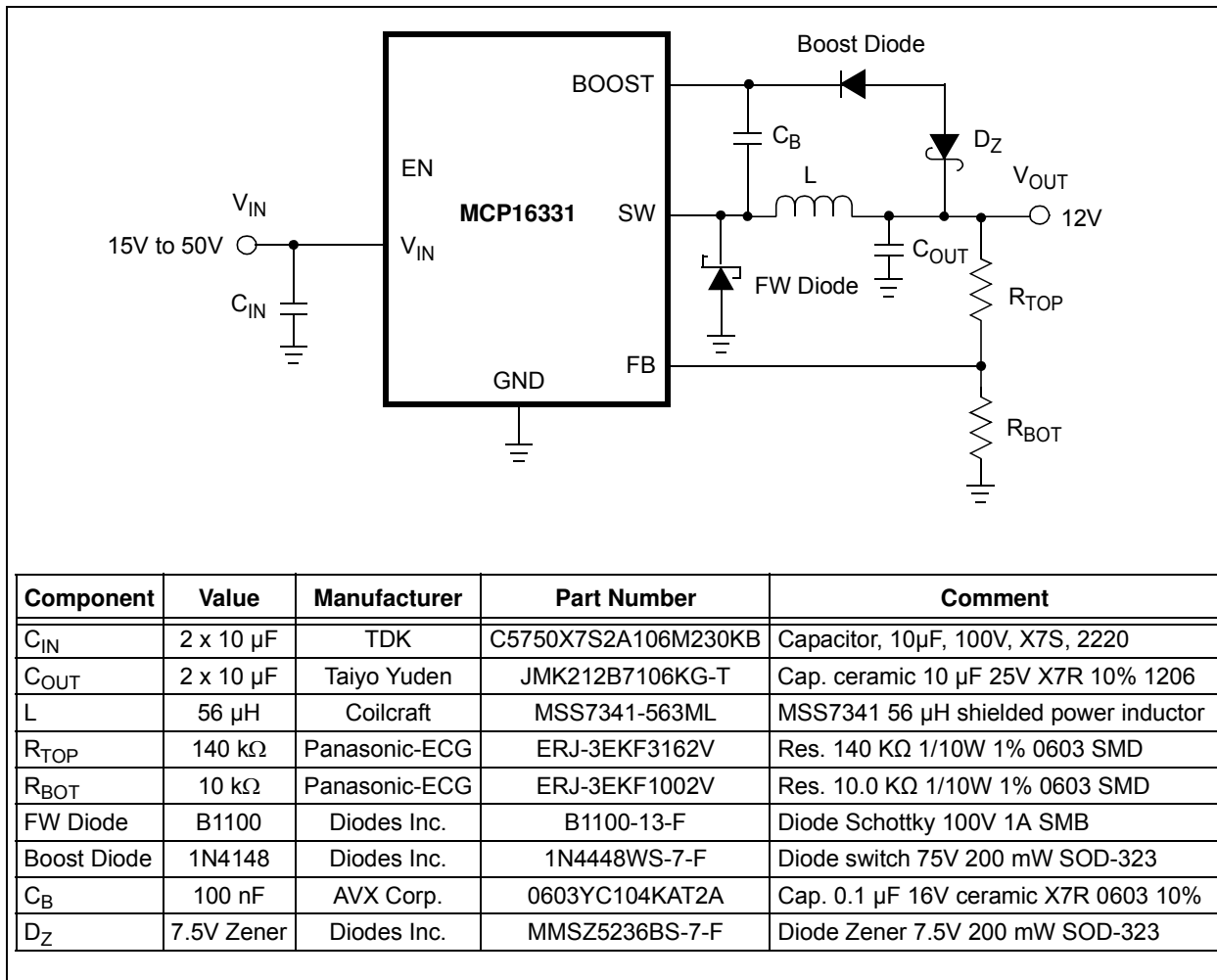
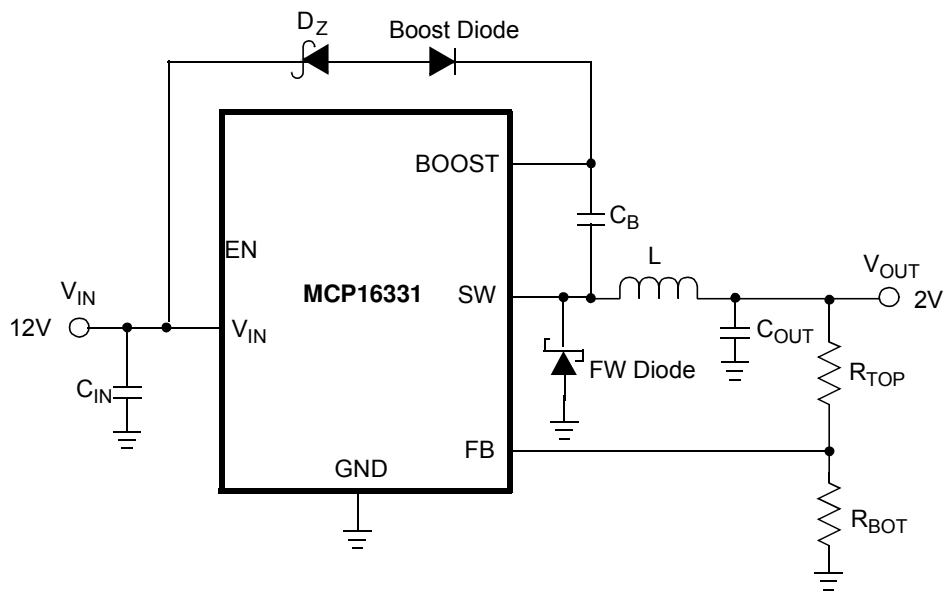


FIGURE 6-2: Typical Application 15V-50V Input; 12V Output.

MCP16331



Component	Value	Manufacturer	Part Number	Comment
C _{IN}	2 x 10 μF	Taiyo Yuden	JMK212B7106KG-T	Cap. ceramic 10 μF 25V X7R 10% 1206
C _{OUT}	22 μF	Taiyo Yuden	JMK316B7226ML-T	Cap. ceramic 22 μF 6.3V X7R 1206
L	10 μH	Coilcraft	MSS4020-103ML	10 μH shielded power inductor
R _{TOP}	15 kΩ	Panasonic-ECG	ERJ-3EKF1502V	Res. 15.0 KΩ 1/10W 1% 0603 SMD
R _{BOT}	10 kΩ	Panasonic-ECG	ERJ-3EKF1002V	Res. 10.0 KΩ 1/10W 1% 0603 SMD
FW Diode	PD3S	Diodes Inc.	PD3S120L-7	Diode Schottky 1A 20V POWERDI323
Boost Diode	1N4148	Diodes Inc.	1N4448WS-7-F	Diode switch 75V 200 mW SOD-323
C _B	100 nF	AVX Corp.	0603YC104KAT2A	Cap. 0.1 μF 16V ceramic X7R 0603 10%
D _Z	7.5V Zener	Diodes Inc.	MMSZ5236BS-7-F	Diode Zener 7.5V 200 mW SOD-323

FIGURE 6-3: Typical Application 12V Input; 2V Output at 500 mA.

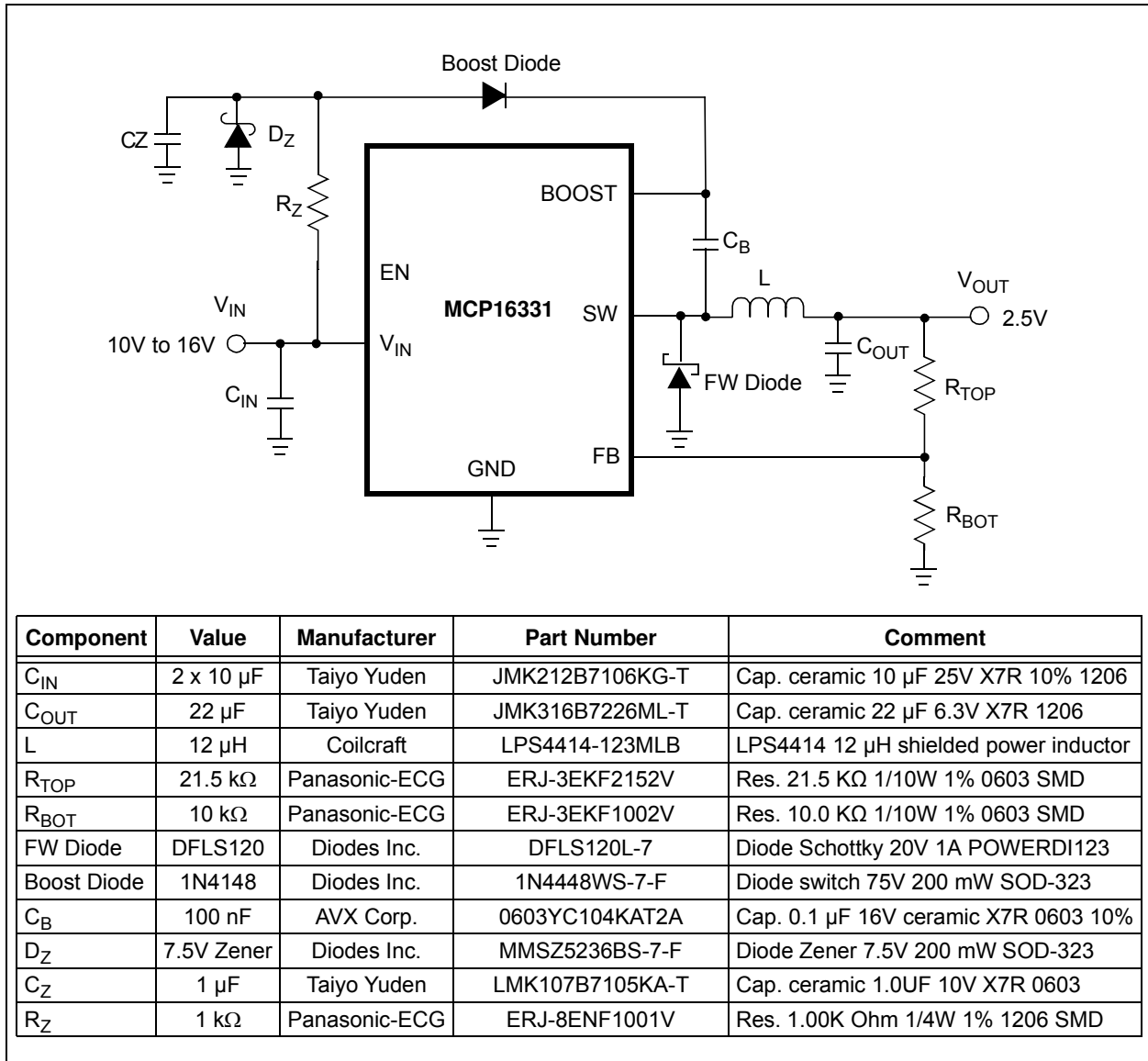


FIGURE 6-4: Typical Application 10V to 16V V_{IN} to 2.5V V_{OUT} .

MCP16331

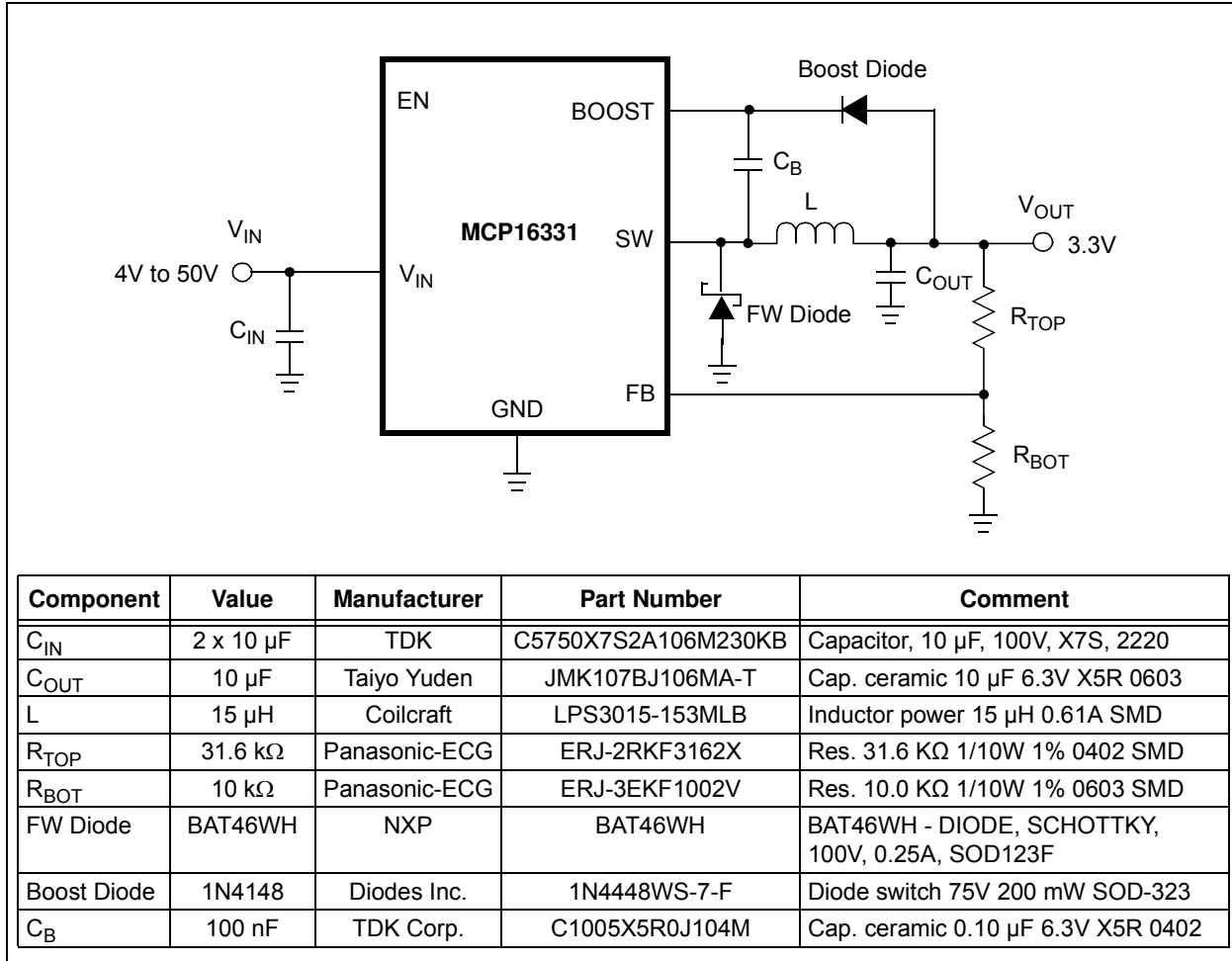
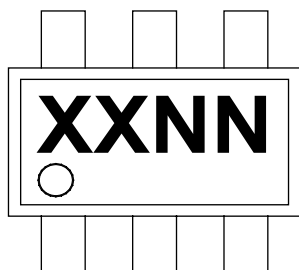


FIGURE 6-5: Typical Application 4V to 50V V_{IN} to 3.3V V_{OUT} at 150 mA.

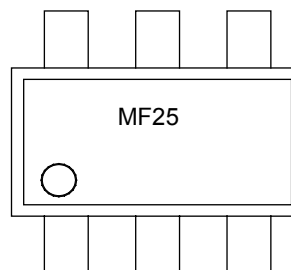
7.0 PACKAGING INFORMATION

7.1 Package Marking Information

6-Lead SOT-23



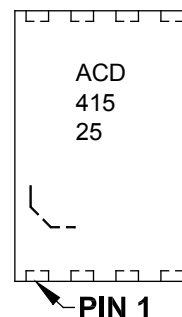
Example



8-Lead TDFN (2x3x0.75 mm)



Example



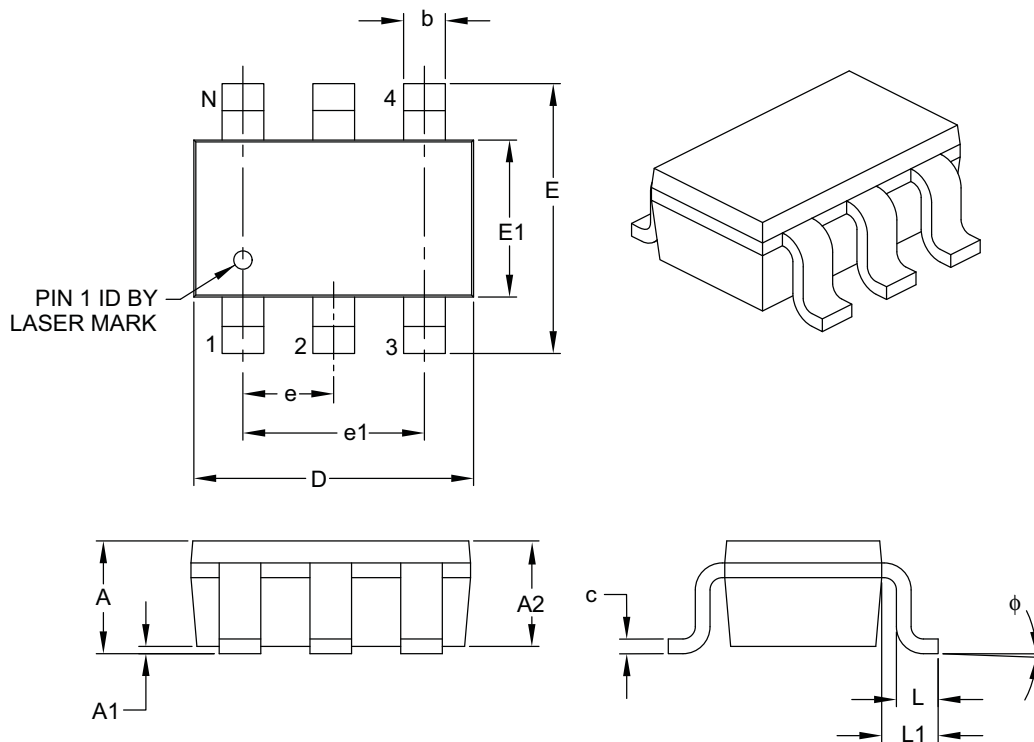
Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

MCP16331

6-Lead Plastic Small Outline Transistor (CH) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	6		
Pitch	e	0.95 BSC		
Outside Lead Pitch	e1	1.90 BSC		
Overall Height	A	0.90	–	1.45
Molded Package Thickness	A2	0.89	–	1.30
Standoff	A1	0.00	–	0.15
Overall Width	E	2.20	–	3.20
Molded Package Width	E1	1.30	–	1.80
Overall Length	D	2.70	–	3.10
Foot Length	L	0.10	–	0.60
Footprint	L1	0.35	–	0.80
Foot Angle	ϕ	0°	–	30°
Lead Thickness	c	0.08	–	0.26
Lead Width	b	0.20	–	0.51

Notes:

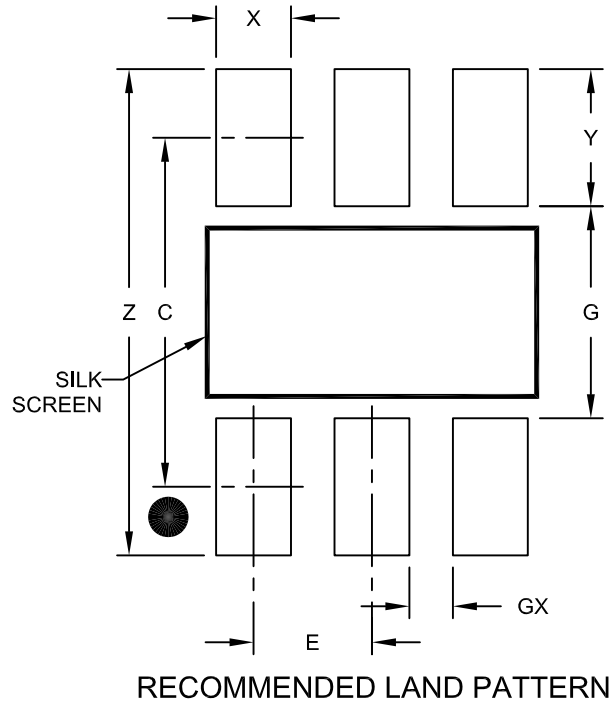
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-028B

6-Lead Plastic Small Outline Transistor (CH) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.95 BSC		
Contact Pad Spacing	C		2.80	
Contact Pad Width (X6)	X			0.60
Contact Pad Length (X6)	Y			1.10
Distance Between Pads	G	1.70		
Distance Between Pads	GX	0.35		
Overall Width	Z			3.90

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

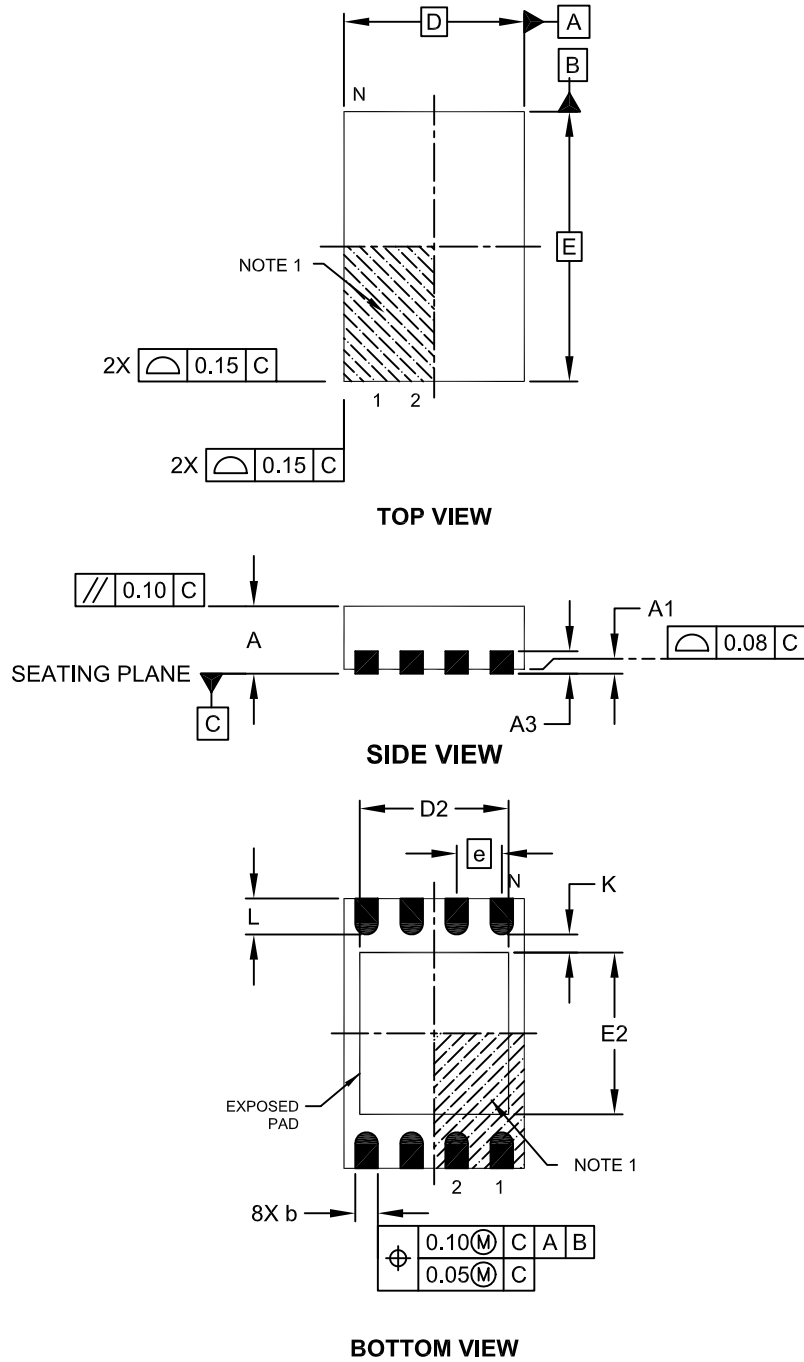
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2028A

MCP16331

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

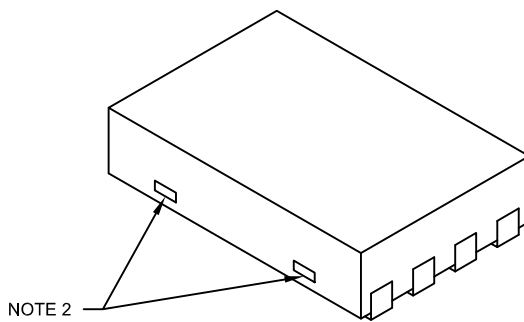
Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Microchip Technology Drawing No. C04-129C Sheet 1 of 2

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	0.50 BSC		
Overall Height	A	0.70	0.75	0.80
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D	2.00 BSC		
Overall Width	E	3.00 BSC		
Exposed Pad Length	D2	1.20	-	1.60
Exposed Pad Width	E2	1.20	-	1.60
Contact Width	b	0.20	0.25	0.30
Contact Length	L	0.25	0.30	0.45
Contact-to-Exposed Pad	K	0.20	-	-

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Package may have one or more exposed tie bars at ends.
3. Package is saw singulated
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

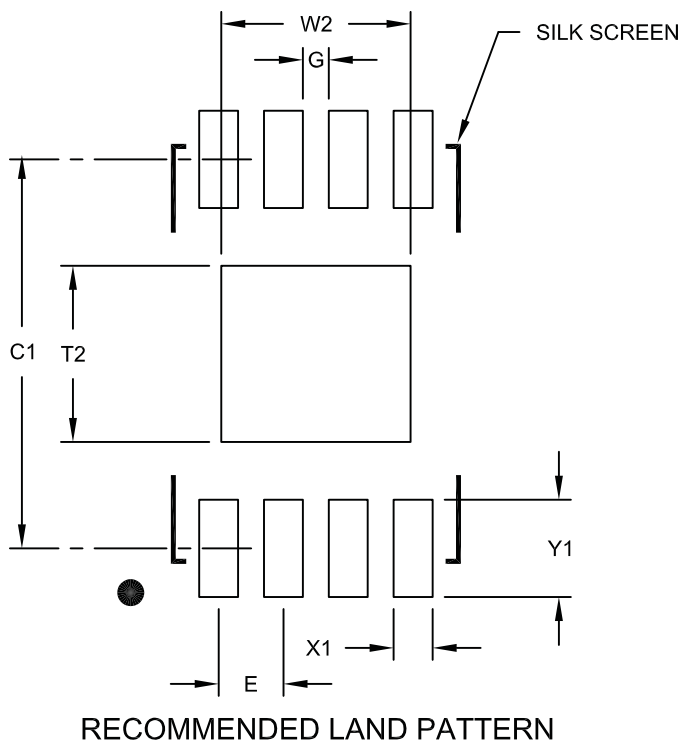
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129C Sheet 2 of 2

MCP16331

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75 mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	0.50 BSC		
Optional Center Pad Width	W2			1.46
Optional Center Pad Length	T2			1.36
Contact Pad Spacing	C1	3.00		
Contact Pad Width (X8)	X1			0.30
Contact Pad Length (X8)	Y1			0.75
Distance Between Pads	G	0.20		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2129A

APPENDIX A: REVISION HISTORY

Revision B (October 2014)

The following is a list of modifications:

1. Added edits to incorporate the AEC-Q100 qualification.

Revision A (June 2014)

- Original Release of this Document.

MCP16331

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO.</u>	<u>XI</u> ⁽¹⁾	<u>X</u>	<u>XX</u>
Device	Tape and Reel Option	Temperature Range	Package
<p>Device:</p> <p>MCP16331: High-Voltage Input Integrated Switch Step-Down Regulator</p> <p>MCP16331T: High-Voltage Input Integrated Switch Step-Down Regulator (Tape and Reel)</p>	<p>Tape and Reel Option:</p> <p>T = Tape and Reel⁽¹⁾</p>	<p>Temperature Range:</p> <p>E = -40°C to +125°C</p>	<p>Package:</p> <p>CH = Plastic SOT-23, 6-lead</p> <p>MNY* = Plastic Dual Flat TDFN, 8-lead</p> <p>* Y = Nickel palladium gold manufacturing designator. Only available on the TDFN package.</p>
<p>Examples:</p> <p>a) MCP16331T-E/CH: Tape and Reel, Extended Temperature, 6LD SOT-23 package</p> <p>b) MCP16331T-E/MNY: Tape and Reel, Extended Temperature, 8LD TDFN package</p>			
<p>Note 1: Tape and Reel identifier only appears in the catalog part number description. This identifier is used for ordering purposes and is not printed on the device package. Check with your Microchip Sales Office for package availability with the Tape and Reel option.</p>			

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as “unbreakable.”

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, dsPIC, FlashFlex, flexPWR, JukeBlox, KEELOQ, KEELOQ logo, Klear, LANCheck, MediaLB, MOST, MOST logo, MPLAB, OptoLyzer, PIC, PICSTART, PIC³² logo, RightTouch, SpyNIC, SST, SST Logo, SuperFlash and UNI/O are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

The Embedded Control Solutions Company and mTouch are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, BodyCom, chipKIT, chipKIT logo, CodeGuard, dsPICDEM, dsPICDEM.net, ECAN, In-Circuit Serial Programming, ICSP, Inter-Chip Connectivity, KlearNet, KlearNet logo, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, MultiTRAK, NetDetach, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, RightTouch logo, REAL ICE, SQI, Serial Quad I/O, Total Endurance, TSHARC, USBCheck, VariSense, ViewSpan, WiperLock, Wireless DNA, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

Silicon Storage Technology is a registered trademark of Microchip Technology Inc. in other countries.

GestIC is a registered trademarks of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2014, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

ISBN: 978-1-63276-694-6

QUALITY MANAGEMENT SYSTEM
CERTIFIED BY DNV
== ISO/TS 16949 ==

Microchip received ISO/TS-16949:2009 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



MICROCHIP

Worldwide Sales and Service

AMERICAS

Corporate Office
2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 480-792-7200
Fax: 480-792-7277
Technical Support:
<http://www.microchip.com/support>
Web Address:
www.microchip.com

Atlanta
Duluth, GA
Tel: 678-957-9614
Fax: 678-957-1455

Austin, TX
Tel: 512-257-3370

Boston
Westborough, MA
Tel: 774-760-0087
Fax: 774-760-0088

Chicago
Itasca, IL
Tel: 630-285-0071
Fax: 630-285-0075

Cleveland
Independence, OH
Tel: 216-447-0464
Fax: 216-447-0643

Dallas
Addison, TX
Tel: 972-818-7423
Fax: 972-818-2924

Detroit
Novi, MI
Tel: 248-848-4000

Houston, TX
Tel: 281-894-5983

Indianapolis
Noblesville, IN
Tel: 317-773-8323
Fax: 317-773-5453

Los Angeles
Mission Viejo, CA
Tel: 949-462-9523
Fax: 949-462-9608

New York, NY
Tel: 631-435-6000

San Jose, CA
Tel: 408-735-9110

Canada - Toronto
Tel: 905-673-0699
Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office
Suites 3707-14, 37th Floor
Tower 6, The Gateway
Harbour City, Kowloon
Hong Kong
Tel: 852-2943-5100
Fax: 852-2401-3431

Australia - Sydney
Tel: 61-2-9868-6733
Fax: 61-2-9868-6755

China - Beijing
Tel: 86-10-8569-7000
Fax: 86-10-8528-2104

China - Chengdu
Tel: 86-28-8665-5511
Fax: 86-28-8665-7889

China - Chongqing
Tel: 86-23-8980-9588
Fax: 86-23-8980-9500

China - Hangzhou
Tel: 86-571-8792-8115
Fax: 86-571-8792-8116

China - Hong Kong SAR
Tel: 852-2943-5100
Fax: 852-2401-3431

China - Nanjing
Tel: 86-25-8473-2460
Fax: 86-25-8473-2470

China - Qingdao
Tel: 86-532-8502-7355
Fax: 86-532-8502-7205

China - Shanghai
Tel: 86-21-5407-5533
Fax: 86-21-5407-5066

China - Shenyang
Tel: 86-24-2334-2829
Fax: 86-24-2334-2393

China - Shenzhen
Tel: 86-755-8864-2200
Fax: 86-755-8203-1760

China - Wuhan
Tel: 86-27-5980-5300
Fax: 86-27-5980-5118

China - Xian
Tel: 86-29-8833-7252
Fax: 86-29-8833-7256

China - Xiamen
Tel: 86-592-2388138
Fax: 86-592-2388130

China - Zhuhai
Tel: 86-756-3210040
Fax: 86-756-3210049

ASIA/PACIFIC

India - Bangalore
Tel: 91-80-3090-4444
Fax: 91-80-3090-4123

India - New Delhi
Tel: 91-11-4160-8631
Fax: 91-11-4160-8632

India - Pune
Tel: 91-20-3019-1500

Japan - Osaka
Tel: 81-6-6152-7160
Fax: 81-6-6152-9310

Japan - Tokyo
Tel: 81-3-6880-3770
Fax: 81-3-6880-3771

Korea - Daegu
Tel: 82-53-744-4301
Fax: 82-53-744-4302

Korea - Seoul
Tel: 82-2-554-7200
Fax: 82-2-558-5932 or
82-2-558-5934

Malaysia - Kuala Lumpur
Tel: 60-3-6201-9857
Fax: 60-3-6201-9859

Malaysia - Penang
Tel: 60-4-227-8870
Fax: 60-4-227-4068

Philippines - Manila
Tel: 63-2-634-9065
Fax: 63-2-634-9069

Singapore
Tel: 65-6334-8870
Fax: 65-6334-8850

Taiwan - Hsin Chu
Tel: 886-3-5778-366
Fax: 886-3-5770-955

Taiwan - Kaohsiung
Tel: 886-7-213-7830

Taiwan - Taipei
Tel: 886-2-2508-8600
Fax: 886-2-2508-0102

Thailand - Bangkok
Tel: 66-2-694-1351
Fax: 66-2-694-1350

EUROPE

Austria - Wels
Tel: 43-7242-2244-39
Fax: 43-7242-2244-393

Denmark - Copenhagen
Tel: 45-4450-2828
Fax: 45-4485-2829

France - Paris
Tel: 33-1-69-53-63-20
Fax: 33-1-69-30-90-79

Germany - Dusseldorf
Tel: 49-2129-3766400

Germany - Munich
Tel: 49-89-627-144-0
Fax: 49-89-627-144-44

Germany - Pforzheim
Tel: 49-7231-424750

Italy - Milan
Tel: 39-0331-742611
Fax: 39-0331-466781

Italy - Venice
Tel: 39-049-7625286

Netherlands - Drunen
Tel: 31-416-690399
Fax: 31-416-690340

Poland - Warsaw
Tel: 48-22-3325737

Spain - Madrid
Tel: 34-91-708-08-90
Fax: 34-91-708-08-91

Sweden - Stockholm
Tel: 46-8-5090-4654

UK - Wokingham
Tel: 44-118-921-5800
Fax: 44-118-921-5820

03/25/14